

IMS T425

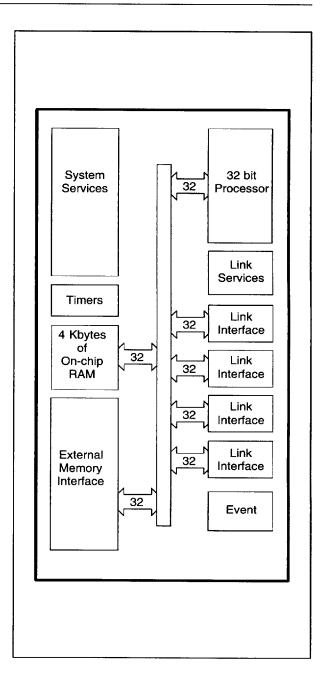
32-bit transputer

FEATURES

- 32 bit architecture
- 40 ns internal cycle time
- 25 MIPS peak instruction rate
- Pin compatible with IMS T805, IMS T800, IMS T400 and IMS T414
- Debugging support
- 4 Kbytes on-chip static RAM
- 100 Mbytes/sec sustained data rate to internal memory
- 4 Gbytes directly addressable external memory
- 33 Mbytes/sec sustained data rate to external memory
- 760 ns response to interrupts
- Four INMOS serial links 5/10/20 Mbits/sec
- High performance graphics support with block move instructions
- Boot from ROM or communication links
- Single 5 MHz clock input
- Single +5V 5% power supply
- Packaging 84 pin PGA / 84 pin PLCC / 100 pin PQFP

APPLICATIONS

- High speed multi processor systems
- High performance graphics processing
- Supercomputers
- Workstations and workstation clusters
- Digital signal processing
- Accelerator processors
- Distributed databases
- System simulation
- Telecommunications
- Robotics
- Fault tolerant systems
- Image processing
- Pattern recognition
- Artificial intelligence



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1 Introduction

The IMS T425 transputer is a 32 bit CMOS microcomputer with graphics support. It has 4 Kbytes on-chip RAM for high speed processing, a configurable memory interface and four standard INMOS communication links. The instruction set achieves efficient implementation of high level languages such as ANSI C and provides direct support for concurrency when using either a single transputer or a network. Procedure calls, process switching and typical interrupt latency are sub-microsecond.

For convenience of description, the IMS T425 operation is split into the basic blocks shown in figure 1.1.

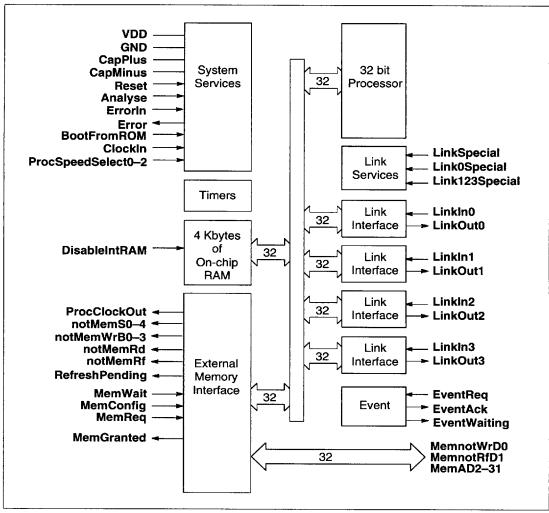


Figure 1.1 IMS T425 block diagram

The processor speed of a device can be pin-selected in stages from 20 MHz up to the maximum allowed for the part. A device running at 25 MHz achieves an instruction throughput of 25 MIPS peak and 12 MIPS sustained.

High performance graphics support is provided by microcoded block move instructions which operate at the speed of memory. The two-dimensional block move instructions provide for contiguous block moves as well as block copying of either non-zero bytes of data only or zero bytes only. Block move instructions can be used to provide graphics operations such as text manipulation, windowing, panning, scrolling and screen updating.

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Cyclic redundancy checking (CRC) instructions are available for use on arbitrary length serial data streams, to provide error detection where data integrity is critical. Another feature of the IMS T425, useful for pattern recognition, is the facility to count bits set in a word.

The IMS T425 can directly access a linear address space of 4 Gbytes. The 32 bit wide memory interface uses multiplexed data and address lines and provides a data rate of up to 4 bytes every 120 nanoseconds (33 Mbytes/sec) for a 25 MHz device. A configurable memory controller provides all timing, control and DRAM refresh signals for a wide variety of mixed memory systems.

System Services include processor reset and bootstrap control, together with facilities for error analysis. Error signals may be daisy-chained in multi-transputer systems.

The standard INMOS communication links allow networks of transputer family products to be constructed by direct point to point connections with no external logic. The IMS T425 links support the standard operating speed of 10 Mbits/sec, but also operate at 5 or 20 Mbits/sec. Each link can transfer data bi-directionally at up to 2.35 Mbytes/sec.

The IMS T425 is pin compatible with the IMS T800 and IMS T805 and can be plugged directly into circuits designed for these devices. It has a number of additions to improve hardware interfacing and to facilitate software initialising and debugging. The improvements have been made in an upwards-compatible manner. Software should be recompiled, although no changes to the source code are necessary.

The transputer is designed to efficiently implement high level languages such as ANSI C andoccam. Access to the transputer at machine level is seldom required, but if necessary refer to the *Transputer Instruction Set – A Compiler Writer's Guide*. A summary of the transputer instruction set can be found in section 11.

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2 Pin designations

Signal names are prefixed by **not** if they are active low, otherwise they are active high. Pinout details for various packages are given in section 9.

Pin	In/Out	Function
VDD, GND		Power supply and return
CapPlus, CapMinus		External capacitor for internal clock power supply
Clockin	in	Input clock
ProcSpeedSelect0-2	in	Processor speed selectors
Reset	in	System reset
Error	out	Error indicator
Errorin	in	Error daisychain input
Analyse	in	Error analysis
BootFromROM	in	Boot from external ROM or from link
DisableIntRAM	in	Disable internal RAM

Table 2.1 IMS T425 system services

Pin	In/Out	Function
ProcClockOut	out	Processor clock
MemnotWrD0	in/out	Multiplexed data bit 0 and write cycle warning
MemnotRfD1	in/out	Multiplexed data bit 1 and refresh warning
MemAD2-31	in/out	Multiplexed data and address bus
notMemRd	out	Read strobe
notMemWrB0-3	out	Four byte-addressing write strobes
notMemS0-4	out	Five general purpose strobes
notMemRf	out	Dynamic memory refresh indicator
RefreshPending	out	Dynamic memory refresh cycle is pending
MemWait	in	Memory cycle extender
MemReq	in	Direct memory access request
MemGranted	out	Direct memory access granted
MemConfig	in	Memory configuration data input

Table 2.2 IMS T425 programmable memory interface

Pin	In/Out	Function
EventReq	in	Event request
EventAck	out	Event request acknowledge
EventWaiting	out	Event input requested by software

Table 2.3 IMS T425 event

Pin	In/Out	Function
Linkln0-3	in	Four serial data input channels
LinkOut0-3 ou		Four serial data output channels
LinkSpecial	in	Select non-standard speed as 5 or 20 Mbits/sec
Link0Special	in	Select special speed for Link 0
Link123Special	in	Select special speed for Links 1, 2, 3

Table 2.4 IMS T425 link



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3 System services

System services include all the necessary logic to initialize and sustain operation of the device. They also include error handling and analysis facilities.

3.1 Power

Power is supplied to the device via the **VDD** and **GND** pins. Several of each are provided to minimize inductance within the package. All supply pins must be connected. The supply must be decoupled close to the chip by at least one 100 nF low inductance (e.g. ceramic) capacitor between **VDD** and **GND**. Four layer boards are recommended; if two layer boards are used, extra care should be taken in decoupling.

Input voltages must not exceed specification with respect to **VDD** and **GND**, even during power-up and power-down ramping, otherwise *latchup* can occur. CMOS devices can be permanently damaged by excessive periods of latchup.

3.2 CapPlus, CapMinus

The internally derived power supply for internal clocks requires an external low leakage, low inductance $1\mu F$ capacitor to be connected between **CapPlus** and **CapMinus**. A ceramic capacitor is preferred, with an impedance less than 3 Ohms between 100 KHz and 10 MHz. If a polarized capacitor is used the negative terminal should be connected to **CapMinus**. Total PCB track length should be less than 50 mm. The connections must not touch power supplies or other noise sources.

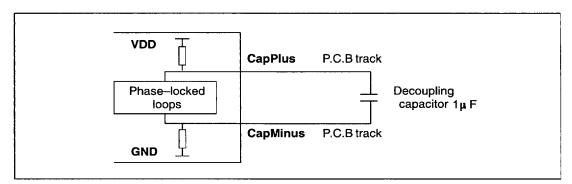


Figure 3.1 Recommended PLL decoupling

3.3 Clockin

Transputerfamily components use a standard clock frequency, supplied by the user on the **ClockIn** input. The nominal frequency of this clock for all transputer family components is 5 MHz, regardless of device type, transputer word length or processor cycle time. High frequency internal clocks are derived from **ClockIn**, simplifying system design and avoiding problems of distributing high speed clocks externally.

A number of transputer devices may be connected to a common clock, or may have individual clocks providing each one meets the specified stability criteria. In a multi-clock system the relative phasing of **ClockIn** clocks is not important, due to the asynchronous nature of the links. Mark/space ratio is unimportant provided the specified limits of **ClockIn** pulse widths are met.

Oscillator stability is important. **ClockIn** must be derived from a crystal oscillator; RC oscillators are not sufficiently stable. **ClockIn** must not be distributed through a long chain of buffers. Clock edges must be monotonic and remain within the specified voltage and time limits.

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Symbol	Parameter	Min	Nom	Max	Units	Notes
TDCLDCH	Clockin pulse width low	40		.,	ns	
TDCHDCL	ClockIn pulse width high	40			ns	
TDCLDCL	Clockin period		200		ns	1,3
TDCerror	ClockIn timing error			0.5	ns	2
TDC1DC2	Difference in ClockIn for 2 linked devices			400	ppm	3
TDCr	ClockIn rise time			10	ns	4
TDCf	Clockin fall time			8	ns	4

Notes

- 1 Measured between corresponding points on consecutive falling edges.
- Variation of individual falling edges from their nominal times.
- 3 This value allows the use of 200ppm crystal oscillators for two devices connected together by a link.

Table 3.1 Input clock timing

Clock transitions must be monotonic within the range VIH to VIL (table 8.3).

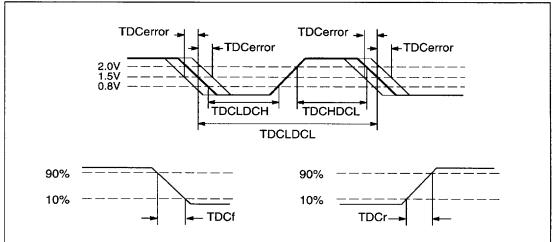


Figure 3.2 ClockIn timing

3.4 ProcSpeedSelect0-2

Processor speed of the IMS T425 is variable in discrete steps. The desired speed can be selected, up to the maximum rated for a particular component, by the three speed select lines ProcSpeedSelect0-2. The pins are tied high or low, according to table 3.2, for the various speeds. The pins are arranged so that the IMS T425 can be plugged directly into a board designed for an IMS T805.

Only six of the possible speed select combinations are currently used; the other two are not valid speed selectors. The frequency of Clockin for the speeds given in the table is 5 MHz.

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ProcSpeed- Select2	ProcSpeed- Select1	ProcSpeed- Select0	Processor Clock Speed MHz	Processor Cycle Time ns	Notes
0	0	0	20.0	50.0	
0	0	1	22.5	44.4	Not supported
0	1	0	25.0	40.0	
0	1	1	30.0	33.3	Not supported
1	0	0	35.0	28.6	Not supported
1	0	1			Invalid
1	1	0	17.5	57.1	Not supported
1	11	1			Invalid

Note: Inclusion of a speed selection in this table does not imply immediate availability.

Table 3.2 Processor speed selection

3.5 Bootstrap

The transputer can be bootstrapped either from a link or from external ROM. To facilitate debugging, **Boot-FromROM** may be dynamically changed but must obey the specified timing restrictions. It is sampled once only by the transputer, before the first instruction is executed after **Reset** is taken low.

If **BootFromROM** is connected high (e.g. to **VDD**) the transputer starts to execute code from the top two bytes in external memory, at address #7FFFFFE. This location should contain a backward jump to a program in ROM. Following this access, **BootFromROM** may be taken low if required. The processor is in the low priority state, and the **W** register points to **MemStart** (page 12).

If **BootFromROM** is connected low (e.g. to **GND**) the transputer will wait for the first bootstrap message to arrive on any one of its links. The transputer is ready to receive the first byte on a link within two processor cycles **TPCLPCL** after **Reset** goes low.

If the first byte received (the control byte) is greater than 1 it is taken as the quantity of bytes to be input. The following bytes, to that quantity, are then placed in internal memory starting at location **MemStart**. Following reception of the last byte the transputer will start executing code at **MemStart** as a low priority process. **BootFromROM** may be taken high after reception of the last byte, if required. The memory space immediately above the loaded code is used as work space. A byte arriving on other links after the control byte has been received and on the bootstrapping link after the last bootstrap byte, will be retained and no acknowledge will be sent until a process inputs from them.

3.6 Peek and poke

Any location in internal or external memory can be interrogated and altered when the transputer is waiting for a bootstrap from link. If the control byte is 0 then eight more bytes are expected on the same link. The first four byte word is taken as an internal or external memory address at which to *poke* (write) the second four byte word. If the control byte is 1 the next four bytes are used as the address from which to *peek* (read) a word of data; the word is sent down the output channel of the same link.

Following such a *peekor poke*, the transputer returns to its previously held state. Any number of accesses may be made in this way until the control byte is greater than 1, when the transputer will commence reading its bootstrap program. Any link can be used, but addresses and data must be transmitted via the same link as the control byte.

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3.7 Reset

Reset can go high with VDD, but must at no time exceed the maximum specified voltage for VIH. After VDD is valid ClockIn should be running for a minimum period TDCVRL before the end of Reset. The falling edge of **Reset** initializes the transputer, triggers the memory configuration sequence and starts the bootstrap routine. Link outputs are forced low during reset; link inputs and EventReq should be held low. Memory request (DMA) is ignored whilst Reset is high but can occur before bootstrap (page 29).

After the end of Reset there will be a delay of 144 periods of ClockIn (figure 3.3). Following this, the MemnotWrD0, MemnotRfD1 and MemAD2-31 pins will be scanned to check for the existence of a preprogrammed memory interface configuration (page 32). This lasts for a further 144 periods of Clockin. Regardless of whether a configuration was found, 36 configuration read cycles will then be performed on external memory using the default memory configuration (page 34), in an attempt to access the external configuration ROM. A delay will then occur, its period depending on the actual configuration. Finally eight complete and consecutive refresh cycles will initialize any dynamic RAM, using the new memory configuration. If the memory configuration does not enable refresh of dynamic RAM the refresh cycles will be replaced by an equivalent delay with no external memory activity.

If BootFromROM is high bootstrapping will then take place immediately, using data from external memory; otherwise the transputer will await an input from any link. The processor will be in the low priority state.

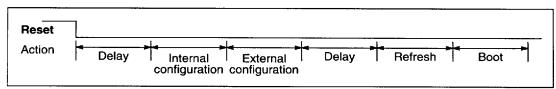


Figure 3.3 IMS T425 post-reset sequence

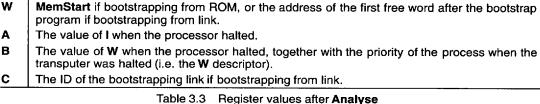
3.8 **Analyse**

If **Analyse** is taken high when the transputer is running, the transputer will halt at the next descheduling point (instructions in out outbyte outword taltwt tin stoperr altwt j lend endp startp). From Analyse being asserted, the processor will halt within three time slice periods plus the time taken for any high priority process to complete. As much of the transputer status is maintained as is necessary to permit analysis of the halted machine. Processor flags Error, HaltOnError and EnableJ0Break are normally cleared at reset on the IMS T425; however, if Analyse is asserted the flags are not altered. Memory refresh continues.

Input links will continue with outstanding transfers. Output links will not make another access to memory for data but will transmit only those bytes already in the link buffer. Providing there is no delay in link acknowledgement, the links should be inactive within a few microseconds of the transputer halting.

Reset should not be asserted before the transputer has halted and link transfers have ceased. When Reset is taken low whilst Analyse is high, neither the memory configuration sequence nor the block of eight refresh cycles will occur; the previous memory configuration will be used for any external memory accesses. If BootFromROM is high the transputer will bootstrap as soon as Analyse is taken low, otherwise it will await a control byte on any link. If Analyse is taken low without Reset going high the transputer state and operation are undefined. After the end of a valid Analyse sequence the registers have the values given in table 3.3.

I	MemStart if bootstrapping from a link, or the external memory bootstrap address if bootstrapping from ROM.
W	MemStart if bootstrapping from ROM, or the address of the first free word after the bootstrap program if bootstrapping from link.
Α	The value of I when the processor halted.
B	The value of W when the processor halted together with the priority of the process when the



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Symbol	Parameter	Min	Nom	Max	Units	Notes
TPVRH	Power valid before Reset	10			ms	
TRHRL	Reset pulse width high	8			Clockin	1
TDCVRL	Clockin running before Reset end	10			ms	2
TAHRH	Analyse setup before Reset	3			ms	
TRLAL	Analyse hold after Reset end	1			ClockIn	1
TBRVRL	BootFromROM setup	0			ms	
TRLBRX	BootFromROM hold after Reset	50			ms	3
TALBRX	BootFromROM hold after Analyse	50			ms	3

Notes

- 1 Full periods of Clockin TDCLDCL required.
- 2 At power-on reset.
- 3 Must be stable until after end of bootstrap period. See Bootstrap section 3.5.

Table 3.4 Reset and Analyse timing

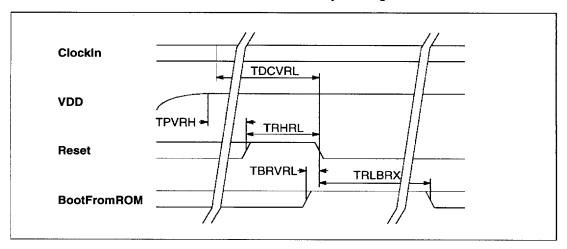


Figure 3.4 Transputer Reset timing with Analyse low

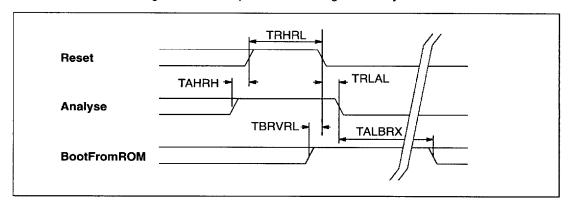


Figure 3.5 Reset and Analyse timing

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3.9 Error, ErrorIn

The **Error** pin carries the OR'ed output of the internal **Error** flag and the **Errorin** input. If **Error** is high it indicates either that **Errorin** is high or that an error was detected in one of the processes. An internal error can be caused, for example, by arithmetic overflow, divide by zero, array bounds violation or software setting the flag directly (page 60). Once set, the **Error** flag is only cleared by executing the instruction *testerr*. The error is not cleared by processor reset, in order that analysis can identify any errant transputer (section 3.8).

A process can be programmed to stop if the **Error** flag is set; it cannot then transmit erroneous data to other processes, but processes which do not require that data can still be scheduled. Eventually all processes which rely, directly or indirectly, on data from the process in error will stop through lack of data. **ErrorIn** does not directly affect the status of a processor in any way.

By setting the **HaltOnError** flag the transputer itself can be programmed to halt if **Error** becomes set. If **Error** becomes set after **HaltOnError** has been set, all processes on that transputer will cease but will not necessarily cause other transputers in a network to halt. Setting **HaltOnError** after **Error** will not cause the transputer to halt; this allows the processor reset and analyse facilities to function with the flags in indeterminate states.

An alternative method of error handling is to have the errant process or transputer cause all transputers to halt. This can be done by 'daisy-chaining' the **ErrorIn** and **Error** pins of a number of processors and applying the final **Error** output signal to the **EventReq** pin of a suitably programmed master transputer (see figure 3.6). Since the process state is preserved when stopped by an error, the master transputer can then use the analyse function to debug the fault. When using such a circuit, note that the **Error** flag is in an indeterminate state on power up; the circuit and software should be designed with this in mind.

Error checks can be removed completely to optimize the performance of a proven program; any unexpected error then occurring will have an arbitrary undefined effect.

If a high priority process pre-empts a low priority one, status of the **Error** and **HaltOnError** flags is saved for the duration of the high priority process and restored at the conclusion of it. Status of both flags is transmitted to the high priority process. Either flag can be altered in the process without upsetting the error status of any complex operation being carried out by the pre-empted low priority process.

In the event of a transputer halting because of **HaltOnError**, the links will finish outstanding transfers before shutting down. If **Analyse** is asserted then all inputs continue but outputs will not make another access to memory for data. Memory refresh will continue to take place.

After halting due to the **Error** flag changing from 0 to 1 whilst **HaltOnError** is set, register I points two bytes past the instruction which set **Error**. After halting due to the **Analyse** pin being taken high, register I points one byte past the instruction being executed. In both cases I will be copied to register **A**.

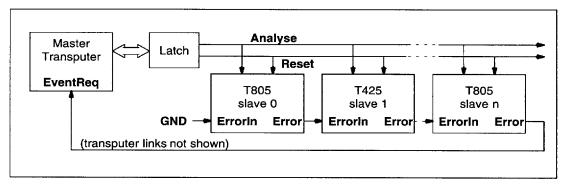


Figure 3.6 Error handling in a multi-transputer system

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4 Memory

The IMS T425 has 4 Kbytes of fast internal static memory for high rates of data throughput. Each internal memory access takes one processor cycle **ProcClockOut** (page 16). The transputer can also access 4 Gbytes of external memory space. Internal and external memory are part of the same linear address space. Internal RAM can be disabled by holding **DisableIntRAM** high. All internal addresses are then mapped to external RAM. This pin should not be altered after **Reset** has been taken low.

IMS T425 memory is byte addressed, with words aligned on four-byte boundaries. The least significant byte of a word is the lowest addressed byte. The bits in a byte are numbered 0 to 7, with bit 0 the least significant. The bytes are numbered from 0, with byte 0 the least significant. In general, wherever a value is treated as a number of component values, the components are numbered in order of increasing numerical significance, with the least significant component numbered 0. Where values are stored in memory, the least significant component value is stored at the lowest (most negative) address.

Internal memory starts at the most negative address #80000000 and extends to #80000FFF. User memory begins at #80000070; this location is given the name **MemStart**. An instruction *Idmemstartval* is provided to obtain the value of **MemStart**.

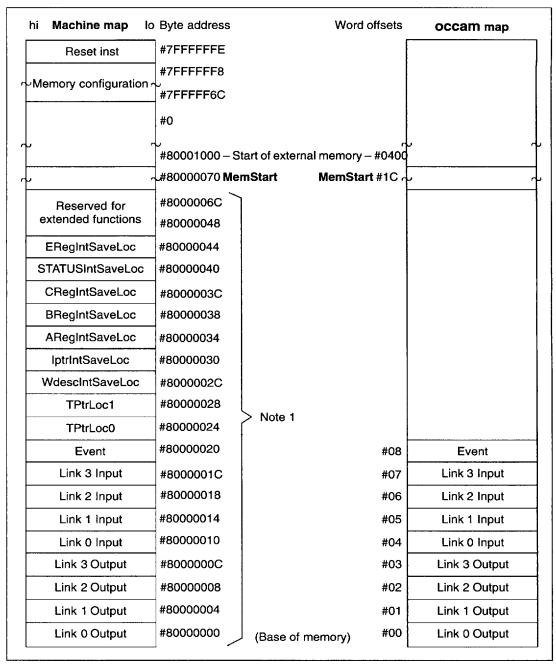
The context of a process in the transputer model involves a workspace descriptor (WPtr) and an instruction pointer (IPtr). WPtr is a word address pointer to a workspace in memory. IPtr points to the next instruction to be executed for the process which is the currently executing process. The context switch performed by the breakpoint instruction swaps the WPtr and IPtr of the currently executing process with the WPtr and IPtr held above MemStart. Two contexts are held above MemStart, one for high priority and one for low priority; this allows processes at both levels to have breakpoints. Note that on bootstrapping from a link, these contexts are overwritten by the loaded code. If this is not acceptable, the values should be peeked from memory before bootstrapping from a link. The reserved area of internal memory below MemStart is used to implement link and event channels.

Two words of memory are reserved for timer use, **TPtrLoc0** for high priority processes and **TPtrLoc1** for low priority processes. They either indicate the relevant priority timer is not in use or point to the first process on the timer queue at that priority level.

Values of certain processor registers for the current low priority process are saved in the reserved intSave-Loc locations when a high priority process pre-empts a low priority one. Other locations are reserved for extended features such as block moves.

External memory space starts at #80001000 and extends up through #00000000 to #7FFFFFF. Memory configuration data and ROM bootstrapping code must be in the most positive address space, starting at #7FFFFF6C and #7FFFFFE respectively. Address space immediately below this is conventionally used for ROM based code.

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Notes

1 These locations are used as auxiliary processor registers and should not be manipulated by the user. Like processor registers, their contents may be useful for implementing debugging tools (Analyse, page 9). For details see the *Transputer Instruction Set – A Compiler Writers' Guide*

Figure 4.1 IMS T425 memory map

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5 External memory interface

The External Memory Interface (EMI) allows access to a 32 bit address space, supporting dynamic and static RAM as well as ROM and EPROM. EMI timing can be configured at **Reset** to cater for most memory types and speeds, and a program is supplied with the Transputer Development System to aid in this configuration.

There are 17 internal configurations which can be selected by a single pin connection (page 32). If none are suitable the user can configure the interface to specific requirements, as shown on page 34.

The external memory cycle is divided into six Tstates with the following functions:

- T1 Address setup time before address valid strobe.
- T2 Address hold time after address valid strobe.
- T3 Read cycle tristate or write cycle data setup.
- T4 Extendable data setup time.
- T5 Read or write data.
- T6 Data hold.

Under normal conditions each **Tstate** may be from one to four periods **Tm** long, the duration being set during memory configuration. The default condition on **Reset** is that all **Tstates** are the maximum four periods **Tm** long to allow external initialisation cycles to read slow ROM.

Period T4 can be extended indefinitely by adding externally generated wait states.

An external memory cycle is always an even number of periods **Tm** in length and the start of **T1** always coincides with a rising edge of **ProcClockOut**. If the total configured quantity of periods **Tm** is an odd number, one extra period **Tm** will be added at the end of **T6** to force the start of the next **T1** to coincide with a rising edge of **ProcClockOut**. This period is designated **E** in configuration diagrams (figure 5.19).

During an internal memory access cycle the external memory interface bus MemAD2-31 reflects the word address used to access internal RAM, MemnotWrD0 reflects the read/write operation and MemnotRfD1 is high; all control strobes are inactive. This is true unless and until a memory refresh cycle or DMA (memory request) activity takes place, when the bus will carry the appropriate external address or data.

The bus activity is not adequate to trace the internal operation of the transputer in full, but may be used for hardware debugging in conjunction with peek and poke (page 8).

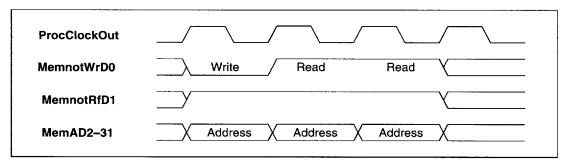


Figure 5.1 IMS 425 bus activity for internal memory cycle

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5.1 Pin functions

5.1.1 MemAD2-31

External memory addresses and data are multiplexed on one bus. Only the top 30 bits of address are output on the external memory interface, using pins **MemAD2-31**. They are normally output only during **Tstates T1** and **T2**, and should be latched during this time. The data bus is 32 bits wide. It uses **MemAD2-31** for the top 30 bits and **MemnotRfD1** and **MemnotWrD0** for the lower two bits.

5.1.2 notMemRd

For a read cycle the read strobe **notMemRd** is low during **T4** and **T5**. Data is read by the transputer on the rising edge of this strobe, and may be removed immediately afterward. If the strobe duration is insufficient it may be extended by adding extra periods **Tm** to either or both of the **Tstates T4** and **T5**. Further extension may be obtained by inserting wait states at the end of **T4**.

5.1.3 MemnotWrD0

During T1 and T2 this pin will be low if the cycle is a write cycle, otherwise it will be high. During Tstates T3 to T6 it becomes bit 0 of the data bus. In both cases it follows the general timing of MemAD2-31.

5.1.4 notMemWrB0-3

Because the transputer uses word addressing, four write strobes are provided; one to write each byte of the word. **notMemWrB0** addresses the least significant byte.

5.1.5 notMemS0-4

To facilitate control of different types of memory and devices, the EMI is provided with five strobe outputs, four of which can be configured by the user. The strobes are conventionally assigned the functions shown in the read and write cycle diagrams, although there is no compulsion to retain these designations.

5.1.6 MemWait

Wait states can be selected by taking **MemWait** high. Externally generated wait states can be added to extend the duration of **T4** indefinitely.

5.1.7 MemnotRfD1

During **T1** and **T2**, this pin is low if the address on **MemAD2-31** is a refresh address, otherwise it is high. During **Tstates T3** to **T6** it becomes bit 1 of the data bus. In both cases it follows the general timing of **MemAD2-31**.

5.1.8 notMemRf

The IMS T425 can be operated with memory refresh enabled or disabled. The selection is made during memory configuration, when the refresh interval is also determined.

5.1.9 RefreshPending

When high, this pin signals that a refresh cycle is pending.

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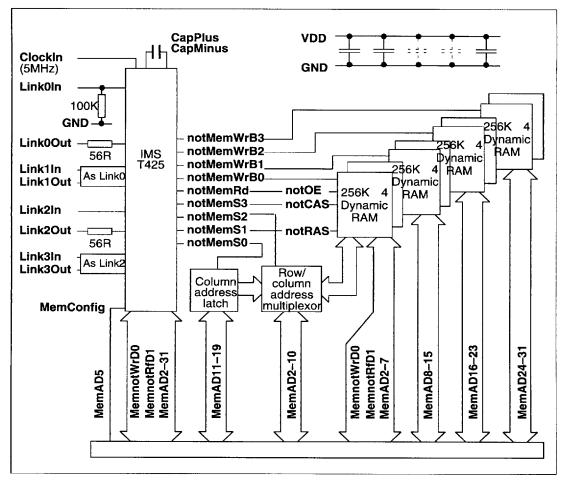


Figure 5.2 IMS T425 application

5.1.10 MemReq, MemGranted

Direct memory access (DMA) can be requested at any time by driving the asynchronous **MemReq** input high. **MemGranted** follows the timing of the bus being tristated and can be used to signal to the device requesting the DMA that it has control of the bus. Note that **MemGranted** changes on the falling edge of **ProcClockOut** and can therefore be sampled to establish control of the bus on the rising edge of **ProcClockOut**.

5.1.11 MemConfig

MemConfig is an input pin used to read configuration data when setting external memory interface (EMI) characteristics.

5.1.12 ProcClockOut

This clock is derived from the internal processor clock, which is in turn derived from **Clockin**. Its period is equal to one internal microcode cycle time, and can be derived from the formula

TPCLPCL = TDCLDCL / PLLx

where TPCLPCL is the ProcClockOut Period, TDCLDCL is the ClockIn Period and PLLx is the phase lock loop factor for the relevant speed part, obtained from the ordering details (Ordering section).

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The time value **Tm** is used to define the duration of **Tstates** and, hence, the length of external memory cycles; its value is exactly half the period of one **ProcClockOut** cycle (0.5***TPCLPCL**), regardless of mark/space ratio of **ProcClockOut**.

Edges of the various external memory strobes coincide with rising or falling edges of **ProcClockOut**. It should be noted, however, that there is a skew associated with each coincidence. The value of skew depends on whether coincidence occurs when the **ProcClockOut** edge and strobe edge are both rising, when both are falling or if either is rising when the other is falling. Timing values given in the strobe tables show the best and worst cases. If a more accurate timing relationship is required, the exact**Tstate** timing and strobe edge to **ProcClockOut** relationships should be calculated and the correct skew factors applied from the edge skew timing table 5.4.

		T425-25			
Symbol	Parameter	Min	Max	Units	Notes
TPCLPCL	ProcClockOut period	38	42	ns	
TPCHPCL	ProcClockOut pulse width high	8.5	23.5	ns	
TPCLPCH	ProcClockOut pulse width low		a	ns	2, 3
Tm	ProcClockOut half cycle	19	21	ns	
TPCstab	ProcClockOut stability		8	%	1

Notes

- Stability is the variation of cycle periods between two consecutive cycles, measured at corresponding points on the cycles.
- 2 a is TPCLPCL TPCHPCL.
- 3 This is a nominal value.

Table 5.1 ProcClockOut

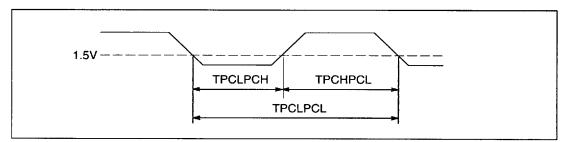


Figure 5.3 IMS T425 ProcClockOut timing

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5.2 Read cycle

Byte addressing is carried out internally by the transputer for read cycles. For a read cycle the read strobe **notMemRd** is low during **T4** and **T5**. Read cycle data may be set up on the data bus at any time after the start of **T3**, but must be valid when the transputer reads it at the end of **T5**. Data may be removed any time during **T6**, but must be off the bus no later than the end of that period.

notMemS0 is a fixed format strobe. Its leading edge is always coincident with the start of **T2** and its trailing edge always coincident with the end of **T5**.

The leading edge of **notMemS1** is always coincident with the start of **T2**, but its duration may be configured to be from zero to 31 periods **Tm**. Regardless of the configured duration, the strobe will terminate no later than the end of **T6**. The strobe is sometimes programmed to extend beyond the normal end of **Tmx**. When wait states are inserted into an EMI cycle the end of **Tmx** is delayed, but the potential active duration of the strobe is not altered. Thus the strobe can be configured to terminate relatively early under certain conditions (page 24). If **notMemS1** is configured to be zero it will never go low.

notMemS2, **notMemS3** and **notMemS4** are identical in operation. They all terminate at the end of **T5**, but the start of each can be delayed from one to 31 periods **Tm** beyond the start of **T2**. If the duration of one of these strobes would take it past the end of **T5** it will stay high. This can be used to cause a strobe to become active only when wait states are inserted. If one of these strobes is configured to zero it will never go low. Figure 5.6 shows the effect of **Wait** on strobes in more detail; each division on the scale is one period **Tm**.

In the read cycle timing diagrams **ProcClockOut** is included as a guide only; it is shown with each **Tstate** configured to one period **Tm**.

		T42	5-25		
Symbol	Parameter	Min	Max	Units	Note
TaZdV	Address tristate to data valid	0		ns	
TdVRdH	Data setup before read	20		ns	
TRdHdX	Data hold after read	0		ns	
TS0LRdL	notMemS0 before start of read	a-4	a+4	ns	1
TS0HRdH	End of read from end of notMemS0	-4	4	ns	
TRdLRdH	Read period	b –3	b +5	ns	2

Notes

- 1 a is total of T2+T3 where T2, T3 can be from one to four periods Tm each in length.
- 2 b is total of T4+Twait+T5 where T4, T5 can be from one to four periods Tm each in length and Twait may be any number of periods Tm in length.

Table 5.2 Read



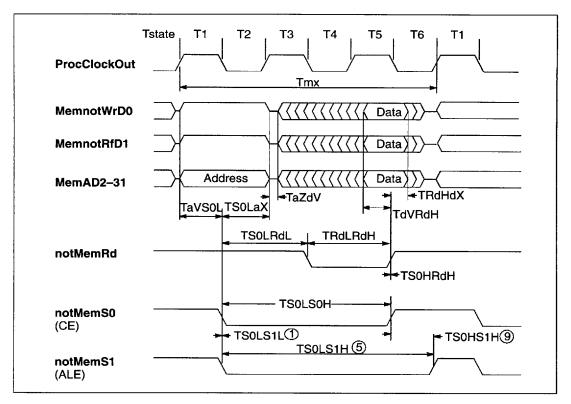


Figure 5.4 IMS T425 external read cycle: static memory

			T42	5-25	
Symbol	n	Parameter	Min	Max	Note
TaVS0L		Address setup before notMemS0	a –8		1
TS0LaX		Address hold after notMemS0	b –8	b +8	2
TS0LS0H		notMemS0 pulse width low	c –5	c +6	3
TS0LS1L	1	notMemS1 from notMemS0	–4	4	
TS0LS1H	5	notMemS1 end from notMemS0	d –3	d +7	4,6
TS0HS1H	9	notMemS1 end from notMemS0 end	e -8	e+4	5,6
TS0LS2L	2	notMemS2 delayed after notMemS0	f-6	f +5	7
TS0LS2H	6	notMemS2 end from notMemS0	c –5	c+7	3
TS0HS2H	10	notMemS2 end from notMemS0 end	-4	7	
TS0LS3L	3	notMemS3 delayed after notMemS0	f –6	f+5	7
TS0LS3H	7	notMemS3 end from notMemS0	c –5	c+7	3
TS0HS3H	11	notMemS3 end from notMemS0 end	-4	7	
TS0LS4L	4	notMemS4 delayed after notMemS0	f–6	f+5	7
TS0LS4H	8	notMemS4 end from notMemS0	c –5	c+7	3
TS0HS4H	12	notMemS4 end from notMemS0 end	-4	7	
Tmx		Complete external memory cycle			8
All timings	in r	nanoseconds (ns).			

Notes

- 1 a is T1 where T1 can be from one to four periods Tm in length.
- 2 b is T2 where T2 can be from one to four periods Tm in length.
- 3 c is total of T2+T3+T4+Twait+T5 where T2, T3, T4, T5 can be from one to four periods Tm each in length and Twait may be any number of periods Tm in length.
- 4 d can be from zero to 31 periods Tm in length.
- 5 e can be from -27 to +4 periods Tm in length.
- 6 If the configuration would cause the strobe to remain active past the end of T6 it will go high at the end of T6. If the strobe is configured to zero periods Tm it will remain high throughout the complete cycle Tmx.
- 7 f can be from zero to 31 periods Tm in length. If this length would cause the strobe to remain active past the end of T5 it will go high at the end of T5. If the strobe value is zero periods Tm it will remain low throughout the complete cycle T1 to T5, going high only for first Tm of T6.
- 8 Tmx is one complete external memory cycle comprising the total of T1+T2+T3+T4+Twait+T5+T6 where T1, T2, T3, T4, T5 can be from one to four periods Tm each in length, T6 can be from one to five periods Tm in length and Twait may be zero or any number of periods Tm in length.

Table 5.3 IMS T425 strobe timing

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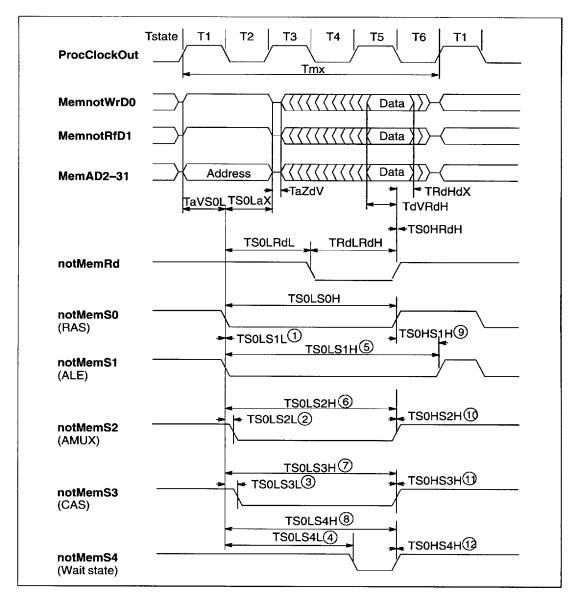


Figure 5.5 IMS T425 external read cycle: dynamic memory

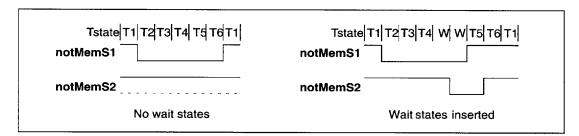


Figure 5.6 IMS T425 effect of wait states on strobes



		T42	T425-25						
Symbol	Parameter	Min	Max						
TPCHS0H	notMemS0 rising from ProcClockOut rising	-6	4						
TPCLS0H	notMemS0 rising from ProcClockOut falling	– 5	10						
TPCHS0L	notMemS0 falling from ProcClockOut rising	– 8	3						
TPCLS0L	notMemS0 falling from ProcClockOut falling	– 5	7						
All timings in nanoseconds (ns).									

Table 5.4 Strobe S0 to ProcClockOut skew

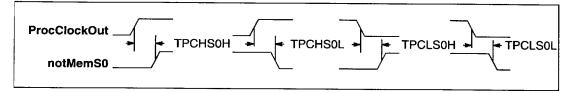


Figure 5.7 IMS T425 skew of notMemS0 to ProcClockOut

5.3 Write cycle

For write cycles the relevant bytes in memory are addressed by the write strobes **notMemWrB0-3**. If a particular byte is not to be written, then the corresponding data outputs are tristated.

For a write cycle pin **MemnotWrD0** will be low during **T1** and **T2**. Write data is placed on the bus at the start of **T3** and removed at the end of **T6**. If **T6** is extended to force the next cycle **Tmx** (page 15) to start on a rising edge of **ProcClockOut**, data will be valid during this time also.

The transputer has both early and late write cycle modes. For a late write cycle the relevant write strobes **notMemWrB0-3** are low during **T4** and **T5**; for an early write they are also low during **T3**. Data should be latched into memory on the rising edge of the strobes in both cases, although it is valid until the end of **T6**. If the strobe duration is insufficient, it may be extended at configuration time by adding extra periods **Tm** to either or both of **Tstates T4** and **T5** for both early and late modes. For an early cycle they may also be added to **T3**. Further extension may be obtained by inserting wait states at the end of **T4**. If the data hold time is insufficient, extra periods **Tm** may be added to **T6** to extend it.

In the write cycle timing diagram **ProcClockOut** is included as a guide only; it is shown with each **Tstate** configured to one period **Tm**. The strobe is inactive during internal memory cycles.

		T42			
Symbol	Parameter	Min	Max	Notes	
TdVWrH	Data setup before write	d-7	d +10	1,5	
TWrHdX	Data hold after write	a –10	a +5	1,2	
TS0LWrL	notMemS0 before start of early write	b –5	b +5	1,3	
	notMemS0 before start of late write	c –5	c +5	1,4	
TS0HWrH	End of write from end of notMemS0	-5	4	1	
TWrLWrH	Early write pulse width	d-4	d +7	1.5	
	Late write pulse width	e -4	e+7	1,6	
All timings	in nanoseconds (ns).				

Notes

- 1 Timing is for all write strobes notMemWrB0-3.
- 2 a is T6 where T6 can be from one to five periods Tm in length.
- 3 b is T2 where T2 can be from one to four periods Tm in length.
- 4 c is total of T2+T3 where T2, T3 can be from one to four periods Tm each in length.
- 5 d is total of T3+T4+Twait+T5 where T3, T4, T5 can be from one to four periods Tm each in length and Twait may be zero or any number of periods Tm in length.
- 6 **e** is total of **T4+Twait+T5** where **T4**, **T5** can be from one to four periods **Tm** each in length and **Twait** may be zero or any number of periods **Tm** in length.

Table 5.5 Write

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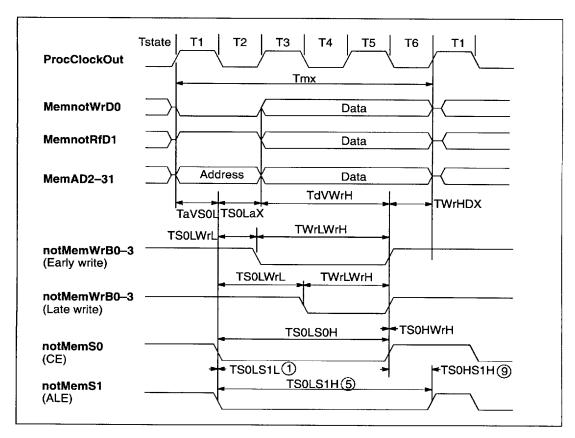


Figure 5.8 IMS T425 external write cycle

5.4 Wait

Taking **MemWait** high with the timing shown (figure 5.9) will extend the duration of **T4**. **MemWait** is sampled close to the falling edge of **ProcClockOut** prior to, but not at, the end of **T4**. By convention, **not-MemS4** is used to synchronize wait state insertion. If this or another strobe is used, its delay should be such as to take the strobe low an even number of periods **Tm** after the start of **T1**, to coincide with a rising edge of **ProcClockOut**.

MemWait may be kept high indefinitely, although if dynamic memory refresh is used it should not be kept high long enough to interfere with refresh timing. **MemWait** operates normally during all cycles, including refresh and configuration cycles. It does not affect internal memory access in any way.

If the start of **T5** would coincide with a falling edge of **ProcClockOut** an extra wait period **Tm (EW)** is generated by the EMI to force coincidence with a rising edge. Rising edge coincidence is only forced if wait states are added, otherwise coincidence with a falling edge is permitted.

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		T42				
Symbol	Parameter	Min	Max	Units	Notes	
TPCLWtH	Wait setup	10		ns	1,2	
TPCLWtL	Wait hold	8		ns	1,2	
TWtLWtH	Delay before re-assertion of Wait	40		ns		

Notes

- 1 ProcClockOut load should not exceed 50pf.
- 2 If wait period exceeds refresh interval, refresh cycles will be lost.

Table 5.6 IMS T425 memory wait

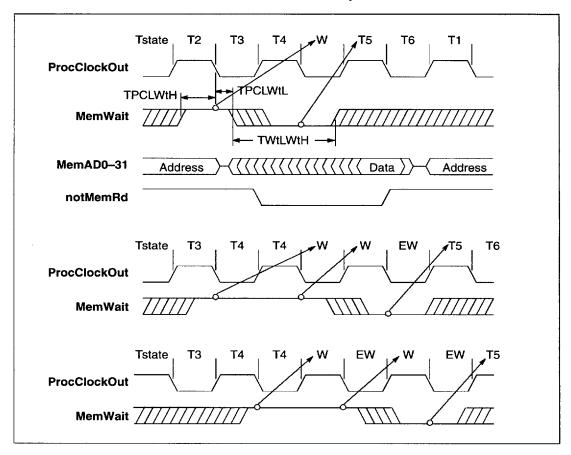


Figure 5.9 IMS T425 memory wait timing

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5.5 Memory refresh

The **RefreshPending** pin is asserted high when the external memory interface is about to perform a refresh cycle. It remains high until the refresh cycle is started by the transputer. The minimum time for the **RefreshPending** pin to be high is for one cycle of **ProcClockOut** (two periods **Tm**), when the EMI was not about to perform a memory read or write. If the EMI was held in the tristate condition with **MemGranted** asserted, then **RefreshPending** will be asserted when the refresh controller in the EMI is ready to perform a refresh. **MemReq** may be re-asserted any time after the commencement of the refresh cycle. **RefreshPending** changes state near the rising edge of **ProcClockOut** and can therefore be sampled by the falling edge of **ProcClockOut**.

If no DMA is active then refresh will be performed following the end of the current internal or external memory cycle. If DMA is active the transputer will wait for DMA to terminate before commencing the refresh cycle. Unlike **MemnotRfD1**, **RefreshPending** is never tristated and can thus be interrogated by the DMA device; the DMA cycle can then be suspended, at the discretion of the DMA device, to allow refresh to take place.

The simple circuit of Figure 5.10 will suspend DMA requests from the external logic when **RefreshPending** is asserted, so that a memory refresh cycle can be performed. DMA is restored on completion of the refresh cycle. The transputer will not perform an external memory cycle other than a refresh cycle, using this method, until the requesting device removes its DMA request.

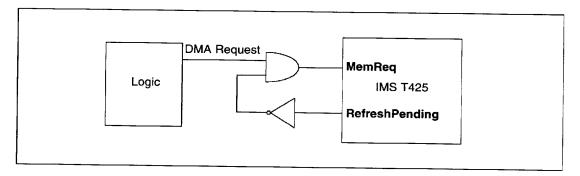


Figure 5.10 IMS T425 refresh with DMA

When refresh is disabled no refresh cycles occur. During the post-Reset period eight dummy refresh cycles will occur with the appropriate timing but with no bus or strobe activity.

A refresh cycle uses the same basic external memory timing as a normal external memory cycle, except that it starts two periods Tm before the start of T1. If a refresh cycle is due during an external memory access, it will be delayed until the end of that external cycle. Two extra periods Tm (periods R in the diagram) will then be inserted between the end of T6 of the external memory cycle and the start of T1 of the refresh cycle itself. The refresh address and various external strobes become active approximately one period Tm before T1. Bus signals are active until the end of T2, whilst Tamber T1 memory cycle and the start of T1 of the period T1 bus signals are active until the end of T2.

For a refresh cycle, MemnotRfD1 goes low before notMemRf goes low and MemnotWrD0 goes high with the same timing as MemnotRfD1. All the address lines share the same timing, but only MemAD2-11 give the refresh address. MemAD12-30 stay high during the address period, whilst MemAD31 remains low. Refresh cycles generate strobes notMemS0-4 with timing as for a normal external cycle, but notMemRd and notMemWrB0-3 remain high. MemWait operates normally during refresh cycles.

Refresh cycles do not interrupt internal memory accesses, although the internal addresses cannot be reflected on the external bus during refresh.

		T42	5-25			
Symbol	Parameter	Min	Max	Units	Notes	
TRfLRfH	Refresh pulse width low	a -2	a +9	ns	1	
TRaVS0L	Refresh address setup before notMemS0	b –12		ns		
TRfLS0L	Refresh indicator setup before notMemS0	b-4	b +6	ns	2	

Notes

- 1 a is total Tmx+Tm.
- 2 b is total T1+Tm where T1 can be from one to four periods Tm in length.

Table 5.7 Memory refresh

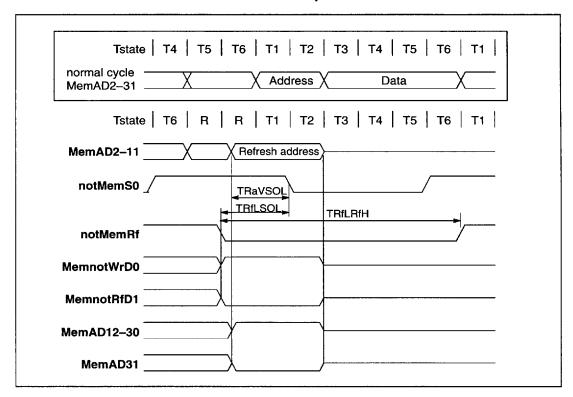


Figure 5.11 IMS T425 refresh cycle timing

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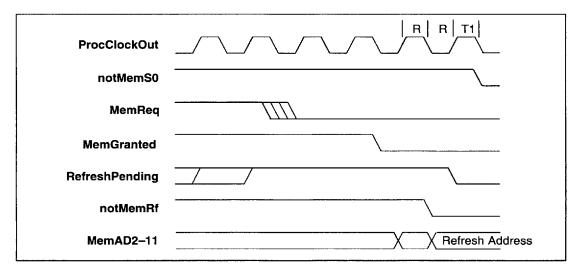


Figure 5.12 IMS T425 refresh pending timing diagram

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5.6 Direct memory access

Direct memory access (DMA) can be requested at any time by driving the asynchronous **MemReq** input high. The transputer samples **MemReq** just before falling edges of **ProcClockOut**. To guarantee taking over the bus immediately following either a refresh or external memory cycle, **MemReq** must be sampled at least four periods **Tm** before the end of **T6**. In the absence of an external memory cycle, the address bus is tristated two periods **Tm** after the **ProcClockOut** rising edge which follows the sample.

Removal of **MemReq** is sampled just before falling edges of **ProcClockOut** and **MemGranted** is removed synchronously with the second falling edge of **ProcClockOut** which follows the sample. If accurate timing of DMA is required, the setup time relative to **ProcClockOut** must be met. Further external bus activity, either refresh, external cycles or reflection of internal cycles, will commence at the next but one rising edge of **ProcClockOut**.

The strobes (notMemS0-4 and notMemWrB0-3) are left in their inactive states during DMA. DMA cannot interrupt a refresh or external memory cycle, and outstanding refresh cycles will occur before the bus is released to DMA. DMA does not interfere with internal memory cycles in any way, although a program running in internal memory would have to wait for the end of DMA before accessing external memory. DMA cannot access internal memory. If DMA extends longer than one refresh interval (Memory Refresh Configuration Coding, table 5.11), the DMA user becomes responsible for refresh (see section 5.5). DMA may also inhibit an internally running program from accessing external memory.

DMA allows a bootstrap program to be loaded into external RAM ready for execution after reset. If Mem-Req is held high throughout reset, MemGranted will be asserted before the bootstrap sequence begins. MemReq must be high at least one period TDCLDCL of ClockIn before Reset. The circuit should be designed to ensure correct operation if Reset could interrupt a normal DMA cycle.

-		T42				
Symbol	Parameter	Min	Max	Units	Note	
TMRHPCL	MemReq setup before ProcClock falling	3	14	ns	1	
TPCLMGH	MemReq response time	77	89	ns	2	
TMRLPCL	Memreq removal before ProcClock falling	4	15			
TPCLMGL	MemReq end response time	40	54	ns		
TADZMGH	Bus tristate before MemGranted	0	22	ns		
TMGLADV	Bus active after end of MemGranted	0	26	ns		

Notes

- 1 Setup time need only be met to guarantee sampling on this edge.
- 2 If an external cycle is active, maximum time could be (1 EMI cycle Tmx)+(1 refresh cycle TRfLRfH)+(6 periods Tm).

Table 5.8 Memory request

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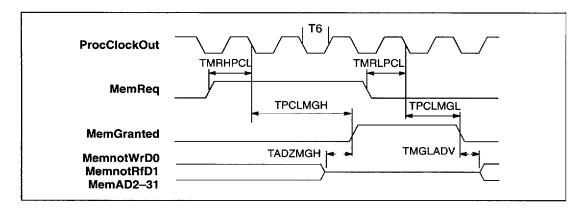


Figure 5.13 IMS T425 memory request timing

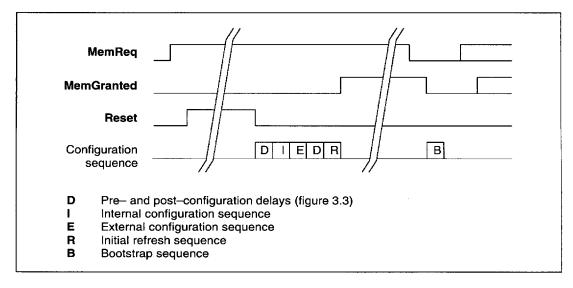


Figure 5.14 IMS T425 DMA sequence at reset

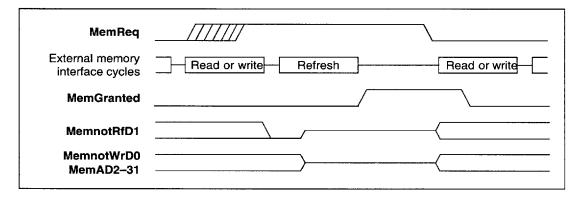


Figure 5.15 IMS T425 operation of MemReq, MemGranted with external, refresh memory cycles



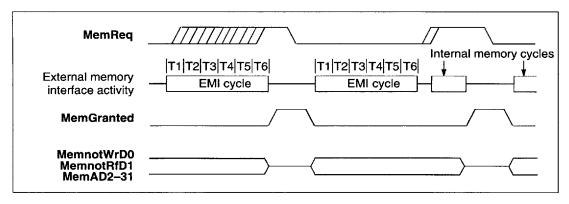


Figure 5.16 IMS T425 operation of MemReq, MemGranted with external, internal memory cycles

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5.7 Memory configuration

MemConfig is an input pin used to read configuration data when setting external memory interface (EMI) characteristics. It is read by the processor on two occasions after **Reset** goes low; first to check if one of the preset internal configurations is required, then to determine a possible external configuration.

5.7.1 Internal configuration

The internal configuration scan comprises 64 periods TDCLDCL of ClockIn during the internal scan period of 144 ClockIn periods. MemnotWrD0, MemnotRfD1 and MemAD2-32 are all high at the beginning of the scan. Starting with MemnotWrD0, each of these lines goes low successively at intervals of two ClockIn periods and stays low until the end of the scan. If one of these lines is connected to MemConfig the preset internal configuration mode associated with that line will be used as the EMI configuration. The default configuration is that defined in the table for MemAD31; connecting MemConfig to VDD will also produce this default configuration. Note that only 17 of the possible configurations are valid, all others remain at the default configuration.

	Duration of each Tstate periods Tm									Write cycle	Refresh interval	Cycle time	
Pin	T1	T2	ТЗ	T4	T5	Т6	s1	s2	s3	s4	type	Clockin cycles	Proc cycles
MemnotWrD0	1	1	1	1	1	1	30	1	3	5	late	72	3
MemnotRfD1	1	2	1	1	1	2	30	1	2	7	late	72	4
MemAD2	1	2	1	1	2	3	30	1	2	7	late	72	5
MemAD3	2	3	1	1	2	3	30	1	3	8	late	72	6
MemAD4	1	1	1	1	1	1	3	1	2	3	early	72	3
MemAD5	1	1	2	1	2	1	5	1	2	3	early	72	4
MemAD6	2	1	2	1	3	1	6	1	2	3	early	72	5
MemAD7	2	2	2	1	3	2	7	1	3	4	early	72	6
MemAD8	1	1	1	1	1	1	30	1	2	3	early	t	3
MemAD9	1	1	2	1	2	1	30	2	5	9	early	†	4
MemAD10	2	2	2	2	4	2	30	2	3	8	late	72	7
MemAD11	3	3	3	3	3	3	30	2	4	13	late	72	9
MemAD12	1	1	2	1	2	1	4	1	2	3	early	72	4
MemAD13	2	1	2	1	2	2	5	1	2	3	early	72	5
MemAD14	2	2	2	1	3	2	6	1	3	4	early	72	6
MemAD15	2	1	2	3	3	3	8	1	2	3	early	72	7
MemAD31	4	4	4	4	4	4	31	30	30	18	late	72	12

† Provided for static RAM only.

Table 5.9 IMS T425 internal configuration coding

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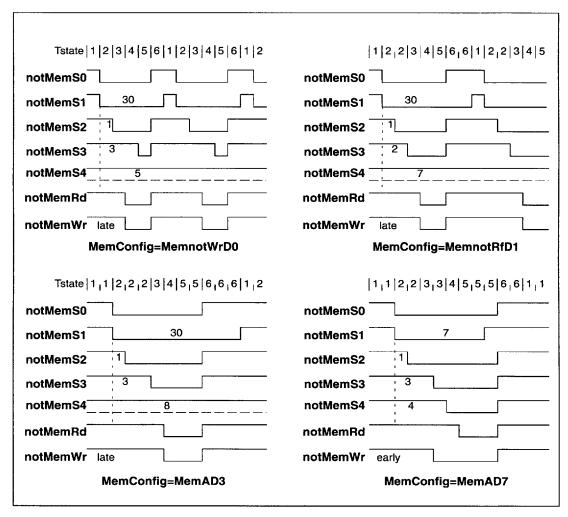


Figure 5.17 IMS T425 internal configuration

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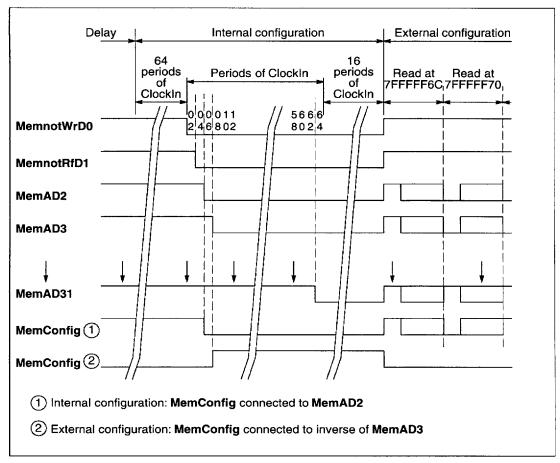


Figure 5.18 IMS T425 internal configuration scan

5.7.2 External configuration

If **MemConfig** is held low until **MemnotWrD0** goes low the internal configuration is ignored and an external configuration will be loaded instead. An external configuration scan always follows an internal one, but if an internal configuration occurs any external configuration is ignored.

The external configuration scan comprises 36 successive external read cycles, using the default EMI configuration preset by **MemAD31**. However, instead of data being read on the data bus as for a normal read cycle, only a single bit of data is read on **MemConfig** at each cycle. Addresses put out on the bus for each read cycle are shown in table 5.10, and are designed to address ROM at the top of the memory map. The table shows the data to be held in ROM; data required at the **MemConfig** pin is the inverse of this.

MemConfig is typically connected via an inverter to MemnotWrD0. Data bit zero of the least significant byte of each ROM word then provides the configuration data stream. By switching MemConfig between various data bus lines up to 32 configurations can be stored in ROM, one per bit of the data bus. MemConfig can be permanently connected to a data line or to GND. Connecting MemConfig to GND gives all Tstates configured to four periods; notMemS1 pulse of maximum duration; notMemS2-4 delayed by maximum; refresh interval 72 periods of Clockin; refresh enabled; late write.

The external memory configuration table 5.10 shows the contribution of each memory address to the 13 configuration fields. The lowest 12 words (#7FFFFF6C to #7FFFF98, fields 1 to 6) define the number of extra periods **Tm** to be added to each **Tstate**. If field 2 is 3 then three extra periods will be added to **T2** to extend it to the maximum of four periods.



5 External memory interface

The next five addresses (field 7) define the duration of **notMemS1** and the following fifteen (fields 8 to 10) define the delays before strobes **notMemS2-4** become active. The five bits allocated to each strobe allow durations of from 0 to 31 periods **Tm**, as described on page 15.

Addresses #7FFFFEC to #7FFFFF4 (fields 11 and 12) define the refresh interval and whether refresh is to be used, whilst the final address (field 13) supplies a high bit to **MemConfig** if a late write cycle is required.

The columns to the right of the coding table show the values of each configuration bit for the four sample external configuration diagrams. Note the inclusion of period E at the end of **T6** in some diagrams. This is inserted to bring the start of the next**Tstate T1** to coincide with a rising edge of **ProcClockOut** (page 16).

Wait states **W** have been added to show the effect of them on strobe timing; they are not part of a configuration. In each case which includes wait states, two wait periods are defined. This shows that if a wait state would cause the start of **T5** to coincide with a falling edge of **ProcClockOut**, another period **Tm** is generated by the EMI to force it to coincide with a rising edge of **ProcClockOut**. This coincidence is only necessary if wait states are added, otherwise coincidence with a falling edge is permitted. Any configuration memory access is only permitted to be extended using wait, up to a total of 14 **ClockIn** periods.

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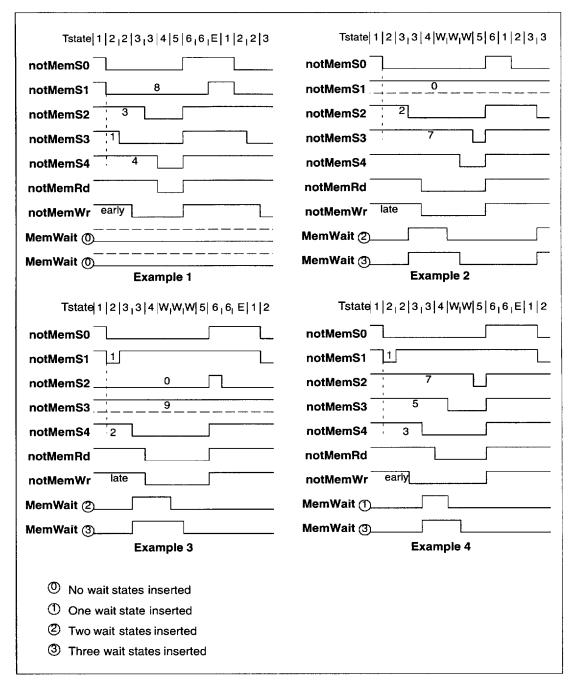


Figure 5.19 IMS T425 external configuration

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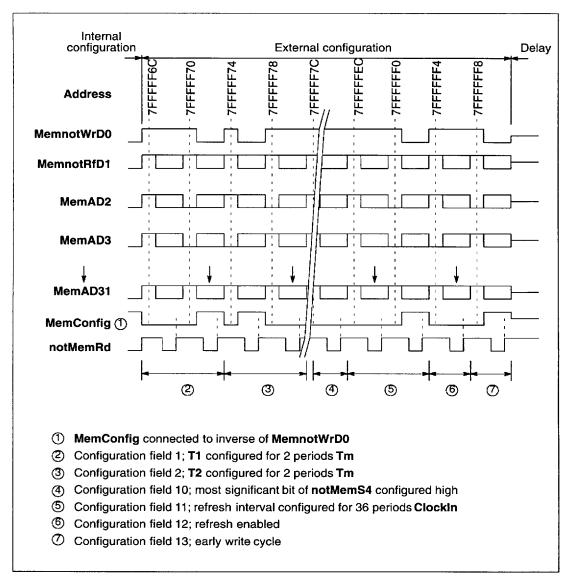


Figure 5.20 IMS T425 external configuration scan

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Scan cycle	Mem AD address	Field	Function	Exan 1	nple di 2	agram 3	4
1	7FFFFF6C	1	T1 least significant bit	0	0	0	0
2	7FFFFF70	1	T1 most significant bit	0	0	0	0
3	7FFFFF74	2	T2 least significant bit	1	0	0	1
4	7FFFFF78	2	T2 most significant bit	0	0	0	0
5	7FFFFF7C	3	T3 least significant bit	1	1	1	1
6	7FFFFF80	3	T3 most significant bit	0	0	0	0
7	7FFFFF84	4	T4 least significant bit	0	0	0	0
8	7FFFFF88	4	T4 most significant bit	0	0	0	0
9	7FFFFF8C	5	T5 least significant bit	0	0	0	0
10	7FFFFF90	5	T5 most significant bit	0	0	0	0
11	7FFFFF94	6	T6 least significant bit	1	0	1	1
12	7FFFFF98	6	T6 most significant bit	0	0	0	0
13	7FFFF9C	7	notMemS1 least significant bit	0	0	1	1
14	7FFFFA0	7		0	0	0	0
15	7FFFFFA4	7	a a	0	0	0	0
16	7FFFFA8	7		1	0	0	0
17	7FFFFAC	7	notMemS1 most significant bit	0	0	0	0
18	7FFFFB0	8	notMemS2 least significant bit	1	0	0	1
19	7FFFFB4	8		1	1	0	1
20	7FFFFB8	8	a a	0	0	0	1
21	7FFFFBC	8		0	0	0	0
22	7FFFFC0	8	notMemS2 most significant bit	0	0	0	0
23	7FFFFC4	9	notMemS3 least significant bit	1	1	1	1
24	7FFFFC8	9		0	1	0	0
25	7FFFFCC	9	a a	0	1	0	1
26	7FFFFD0	9		0	0	1	0
27	7FFFFD4	9	notMemS3 most significant bit	0	0	0	0
28	7FFFFFD8	10	notMemS4 least significant bit	0	0	0	1
29	7FFFFFDC	10		0	1	1	1
30	7FFFFFE0	10	a a	1	1	0	0
31	7FFFFE4	10		0	0	0	0
32	7FFFFE8	10	notMemS4 most significant bit	0	0	0	0
33	7FFFFEC	11	Refresh Interval least significant bit	-	-	-	-
34	7FFFFFF0	11	Refresh Interval most significant bit	-	j -	-	-
35	7FFFFFF4	12	Refresh Enable	-	-	-	-
36	7FFFFFF8	13	Late Write	0	1	1	0

Table 5.10 IMS T425 external configuration coding

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Refresh interval	Interval in µs	Field 11 encoding	Complete cycle (ms)
18	3.6	00	0.922
36	7.2	01	1.843
54	10.8	10	2.765
72	14.4	11	3.686

Table 5.11 IMS T425 memory refresh configuration coding

Refresh intervals are in periods of Clockin and Clockin frequency is 5 MHz:

Interval = 18 * 200 = 3600 ns

Refresh interval is between successive incremental refresh addresses. Complete cycles are shown for 256 row DRAMS.

		T425-25		
Symbol	Parameter	Min	Max	Units
TMCVRdH	MemConfig data setup	20		ns
TRdHMCX	MemConfig data hold			ns
TS0LRdH	notMemS0 to configuration data read	308	332	ns

Table 5.12 Memory configuration

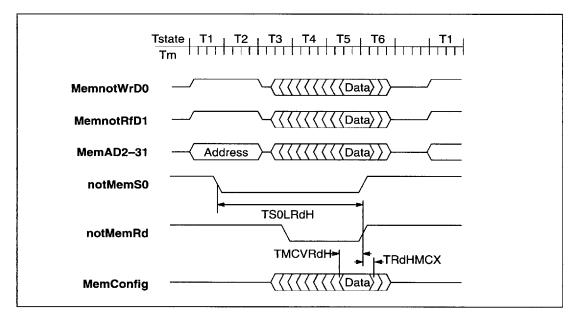


Figure 5.21 IMS T425 external configuration read cycle timing

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6 Events

EventReq and **EventAck** provide an asynchronous handshake interface between an external event and an internal process. When an external event takes **EventReq** high the external event channel (additional to the external link channels) is made ready to communicate with a process. When both the event channel and the process are ready the processor takes **EventAck** high and the process, if waiting, is scheduled. **EventAck** is removed after **EventReq** goes low.

EventWaiting is asserted high by the transputer when a process executes an input on the event channel; typically with the occam EVENT? ANY instruction. It remains high whilst the transputer is waiting for or servicing **EventReq** and is returned low when **EventAck** goes high. The **EventWaiting** pin changes near the falling edge of **ProcClockOut** and can therefore be sampled by the rising edge of **ProcClockOut**.

The **EventWaiting** pin can only be asserted by executing an *in* instruction on the event channel. The **EventWaiting** pin is not asserted high when an enable channel (*enbc*) instruction is executed on the Event channel (during an ALT construct in occam, for example). The **EventWaiting** pin can be asserted by executing the occam input on the event channel (such as EVENT? ANY), provided that this does not occur as a guard in an alternative process. The **EventWaiting** pin can not be used to signify that an alternative process (ALT) is waiting on an input from the event channel.

EventWaiting allows a process to control external logic; for example, to clock a number of inputs into a memory mapped data latch so that the event request type can be determined.

Only one process may use the event channel at any given time. If no process requires an event to occur **EventAck** will never be taken high. Although **EventReq** triggers the channel on a transition from low to high, it must not be removed before **EventAck** is high. **EventReq** should be low during **Reset**; if not it will be ignored until it has gone low and returned high. **EventAck** is taken low when **Reset** occurs.

If the process is a high priority one and no other high priority process is running, typical latency is 19 full processor cycles **TCPLCPL** (38 **Tm**), and maximum latency (assuming all memory accesses are internal) is 58 full processor cycles (116 **Tm**). Setting a high priority task to wait for an event input allows the user to interrupt a transputer program running at low priority. The time taken from asserting **EventReq** to the execution of the microcode interrupt handler in the CPU is four cycles. The following functions take place during the four cycles:

- Cycle 1 Sample EventReq at pad on the rising edge of ProcClockOut and synchronize.
- Cycle 2 Edge detect the synchronized EventReg and form the interrupt request.
- Cycle 3 Sample interrupt vector for microcode ROM in the CPU.
- **Cycle 4** Execute the interrupt routine for the event rather than the next instruction.

		T42		
Symbol	Parameter	Min	Max	Units
TVHKH	EventReq response	0		ns
TKHVL	EventReq hold	0		ns
TVLKL	Delay before removal of EventAck	0	127	ns
TKLVH	Delay before re-assertion of EventReq	0	ļ	ns
TKHEWL	EventAck to end of EventWaiting	0		ns

Table 6.1 Event timing

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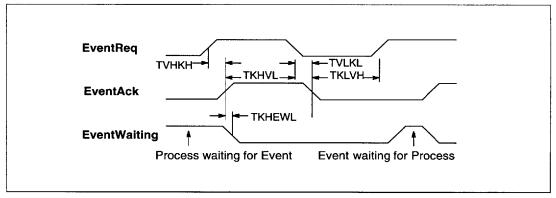


Figure 6.1 IMS T425 event timing

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7 Links

Four identical INMOS bi-directional serial links provide synchronized communication between processors and with the outside world. Each link comprises an input channel and output channel. A link between two transputers is implemented by connecting a link interface on one transputer to a link interface on the other transputer. Every byte of data sent on a link is acknowledged on the input of the same link, thus each signal line carries both data and control information.

The quiescent state of a link output is low. Each data byte is transmitted as a high start bit followed by a one bit followed by eight data bits followed by a low stop bit. The least significant bit of data is transmitted first. After transmitting a data byte the sender waits for the acknowledge, which consists of a high start bit followed by a zero bit. The acknowledge signifies both that a process was able to receive the acknowledged data byte and that the receiving link is able to receive another byte. The sending link reschedules the sending process only after the acknowledge for the final byte of the message has been received.

The IMS T425 links allow an acknowledge packet to be sent before the data packet has been fully received. This overlapped acknowledge technique is fully compatible with all other INMOS transputer links.

The IMS T425 links support the standard INMOS communication speed of 10 Mbits/sec. In addition they can be used at 5 or 20 Mbits/sec. Links are not synchronized with **ClockIn** or **ProcClockOut** and are insensitive to their phases. Thus links from independently clocked systems may communicate, providing only that the clocks are nominally identical and within specification.

Links are TTL compatible and intended to be used in electrically quiet environments, between devices on a single printed circuit board or between two boards via a backplane. Direct connection may be made between devices separated by a distance of less than 300 millimeters. For longer distances a matched 100 ohm transmission line should be used with series matching resistors **RM**, see figure 7.5. When this is done the line delay should be less than 0.4 bit time to ensure that the reflection returns before the next data bit is sent.

Buffers may be used for very long transmissions, see figure 7.6. If so, their overall propagation delay should be stable within the skew tolerance of the link, although the absolute value of the delay is immaterial.

Link speeds can be set by LinkSpecial, Link0Special and Link123Special. The link 0 speed can be set independently. Table 7.1 shows uni-directional and bi-directional data rates in Kbytes/sec for each link speed; LinknSpecial is to be read as Link0Special when selecting link 0 speed and as Link123Special for the others. Data rates are quoted for a transputer using internal memory, and will be affected by a factor depending on the number of external memory accesses and the length of the external memory cycle.

Link	Linkn		Kbytes/sec	
Special	Special	Mbits/sec	Uni	Bi
0	0	10	910	1250
0	1	5	450	670
1	0	10	910	1250
1	1	20	1740	2350

Table 7.1 Speed settings for transputer links

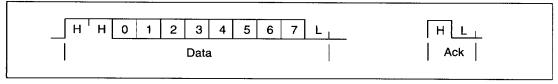


Figure 7.1 IMS T425 link data and acknowledge packets

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Symbol	Parameter		Min	Nom	Max	Units	Notes
TJQr	LinkOut rise time				20	ns	
TJQf	LinkOut fall time				10	ns	
TJDr	Linkin rise time				20	ns	
TJDf	Linkin fall time			1	20	ns	
TJQJD	Buffered edge delay		0]		ns	
TJBskew	Variation in TJQJD	20 Mbits/s			3	ns	1
		10 Mbits/s			10	ns	1
		5 Mbits/s			30	ns	1
CLIZ	Linkin capacitance	@ f=1MHz			7	pF	
CLL	LinkOut load capacitance				50	pF	
RM	Series resistor for 100ohm	transmission		56		ohms	

Notes

1 This is the variation in the total delay through buffers, transmission lines, differential receivers etc., caused by such things as short term variation in supply voltages and differences in delays for rising and falling edges.

Table 7.2 Link timing

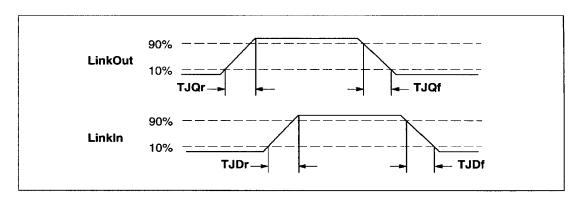


Figure 7.2 IMS T425 link timing

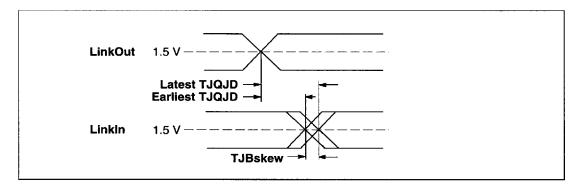


Figure 7.3 IMS T425 buffered link timing



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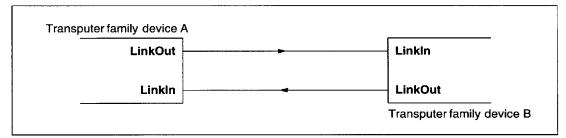


Figure 7.4 IMS T425 links directly connected

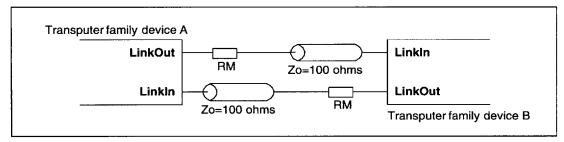


Figure 7.5 IMS T425 links connected by transmission line

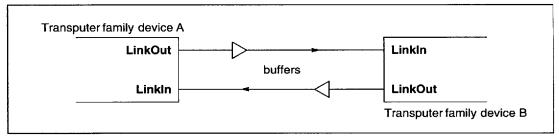


Figure 7.6 IMS T425 links connected by buffers

8 Electrical specifications

8.1 Absolute maximum ratings

SYMBOL	PARAMETER	MIN	MAX	UNITS	NOTES
VDD	DC supply voltage	0	7.0	V	1,2,3
Vı, Vo	Voltage on input and output pins	-0.5	VDD+0.5	V	1,2,3
li I	Input current		25	mA	4
tosc	Output short circuit time (one pin)		1	s	2
Ts	Storage temperature	-65	150	∘c	2
TA	Ambient temperature under bias	- 55	125	∘c	2
PDmax	Maximum allowable dissipation		2	w	

Notes

- 1 All voltages are with respect to GND.
- 2 This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operating sections of this specification is not implied. Stresses greater than those listed may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 3 This device contains circuitry to protect the inputs against damage caused by high static voltages or electrical fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than the absolute maximum rated voltages to this high impedance circuit. Unused inputs should be tied to an appropriate logic level such as VDD or GND.
- 4 The input current applies to any input or output pin and applies when the voltage on the pin is between GND and VDD.

Table 8.1 Absolute maximum ratings

8.2 Operating conditions

SYMBOL	PARAMETER	MIN	MAX	UNITS	NOTES
VDD	DC supply voltage	4.75	5.25	V	1
Vı, Vo	Input or output voltage	0	VDD	V	1,2
CL	Load capacitance on any pin		60	pF	3
TA	Operating temperature range	0	70	°C	4

Notes

- 1 All voltages are with respect to GND.
- 2 Excursions beyond the supplies are permitted but not recommended; see DC characteristics.
- 3 Excluding LinkOut load capacitance.
- 4 Air flow rate 400 linear ft/min transverse air flow.

Table 8.2 Operating conditions



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8.3 DC electrical characteristics

SYMBOL	PARAM	PARAMETER		MAX	UNITS	NOTES
ViH	High level input voltage		2.0	VDD+0.5	V	1,2
VIL	Low level input voltage		-0.5	0.8	V	1,2
li .	Input current	@ GND <vi<vdd< td=""><td></td><td>10</td><td>μА</td><td>1,2</td></vi<vdd<>		10	μА	1,2
Vон	Output high voltage	@ IOH=2mA	VDD-1		V	1,2
VOL	Output low voltage	@ IOL=4mA		0.4	V	1,2
loz	Tristate output current	@ GND <v0<vdd< td=""><td></td><td>10</td><td>μΑ</td><td>1,2</td></v0<vdd<>		10	μΑ	1,2
PD	Power dissipation			1	w	2,3
CIN	Input capacitance	@ f=1MHz		7	pF	
Coz	Output capacitance	@ f=1MHz		10	pF	

Notes

- 1 All voltages are with respect to GND.
- 2 Parameters for IMS T425-S measured at 4.75V<VDD<5.25V and 0°C<Ta<70°C. Input clock frequency = 5 MHz.</p>
- 3 Power dissipation varies with output loading and program execution. Power dissipation for processor operating at 20 MHz.

Table 8.3 DC characteristics

8.4 Equivalent circuits

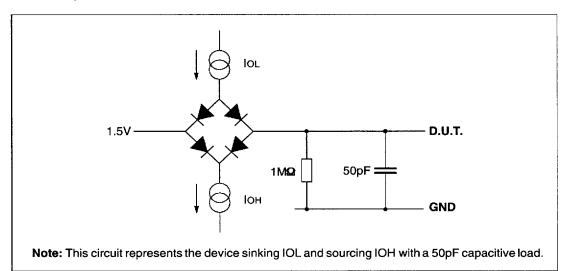


Figure 8.1 Load circuit for AC measurements

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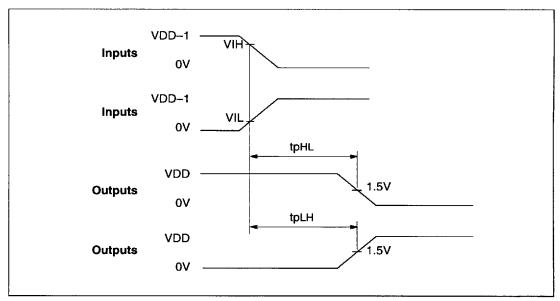


Figure 8.2 AC measurements timing waveforms

8.5 AC timing characteristics

Symbol	Parameter		Max	Units	Notes
TDr	Input rising edges	2	20	ns	1, 2
TDf	Input falling edges	2	20	ns	1, 2
TQr	Output rising edges		25	ns	1
TQf	Output falling edges		15	ns	1
TS0LaX	Address hold after notMemS0	a –8	a +8	ns	3

Notes

- 1 Non-link pins; see section on links.
- 2 All inputs except Clockin; see section on Clockin.
- 3 a is T2 where T2 can be from one to four periods Tm in length. Address lines include MemnotWrD0, MemnotRfD1, MemAD2-31.

Table 8.4 Input and output edges

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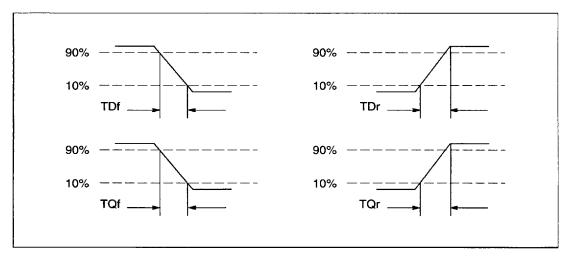


Figure 8.3 IMS T425 input and output edge timing

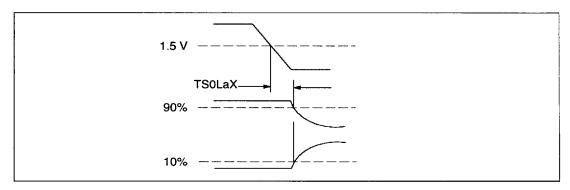


Figure 8.4 IMS T425 tristate timing relative to notMemS0

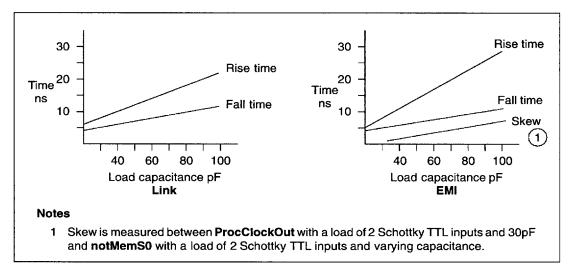


Figure 8.5 Typical rise/fall times

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8.6 Power rating

Internal power dissipation (P_{INT}) of transputer and peripheral chips depends on **VDD**, as shown in figure 8.6. P_{INT} is substantially independent of temperature.

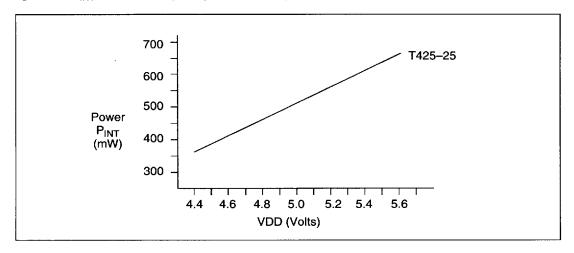


Figure 8.6 IMS T425 internal power dissipation vs VDD

Total power dissipation (PD) of the chip is

$$P_D = P_{INT} + P_{IO}$$

where P_{IO} is the power dissipation in the input and output pins; this is application dependent.

Internal working temperature T_J of the chip is

$$T_J = T_A + \theta_{JA} * P_D$$

where T_A is the external ambient temperature in ${}^{\circ}C$ and θ_{JA} is the junction-to-ambient thermal resistance in ${}^{\circ}C/W$.

Further information about device thermal characteristics can be found in section 9.4.

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9 Package details

9.1 84 pin grid array package

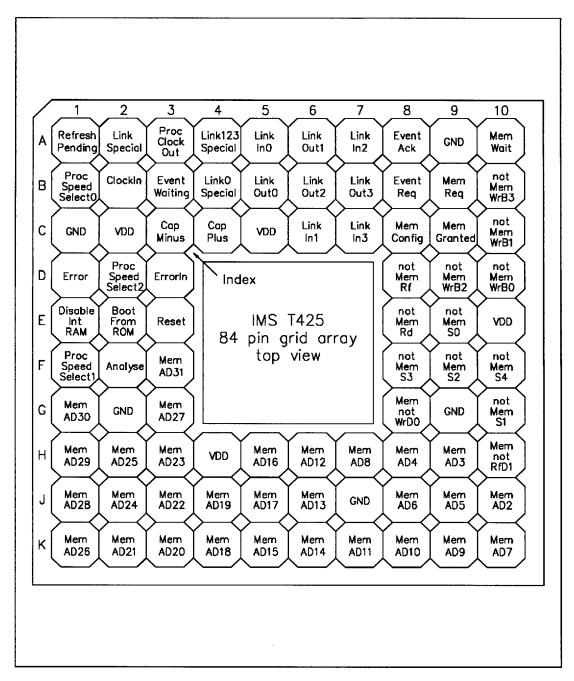


Figure 9.1 IMS T425 84-pin grid array (PGA) package pinout

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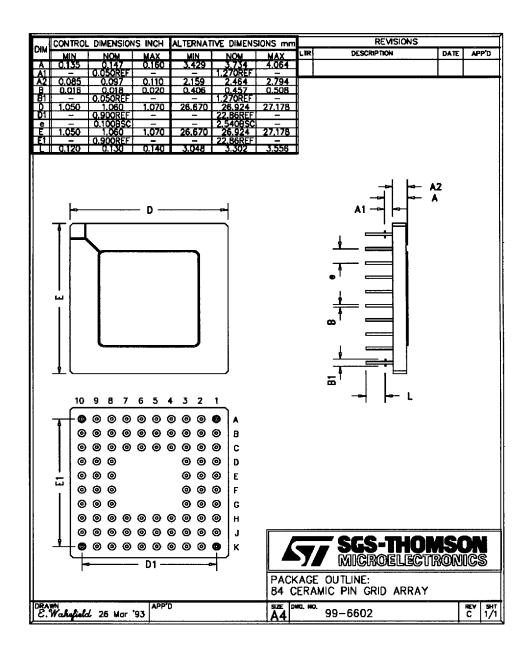


Figure 9.2 IMS T425 84-pin grid array (PGA) package dimensions

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9.2 84 pin PLCC package

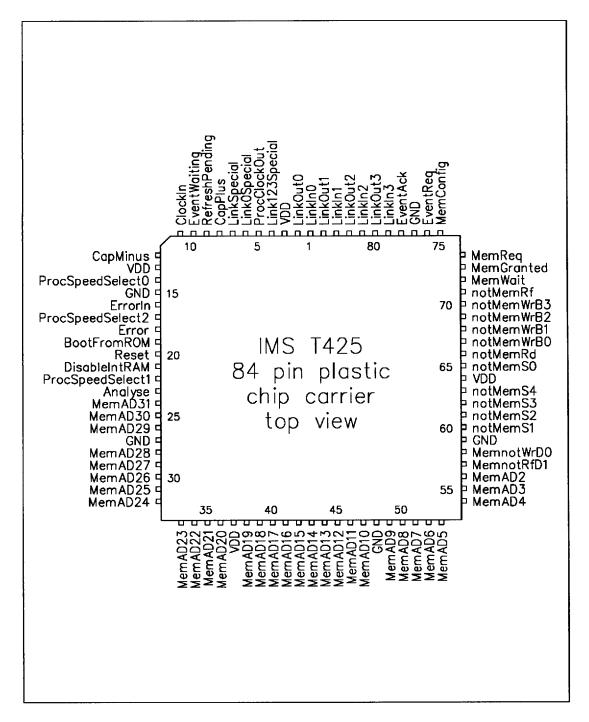


Figure 9.3 IMS T425 84-pin PLCC package pinout

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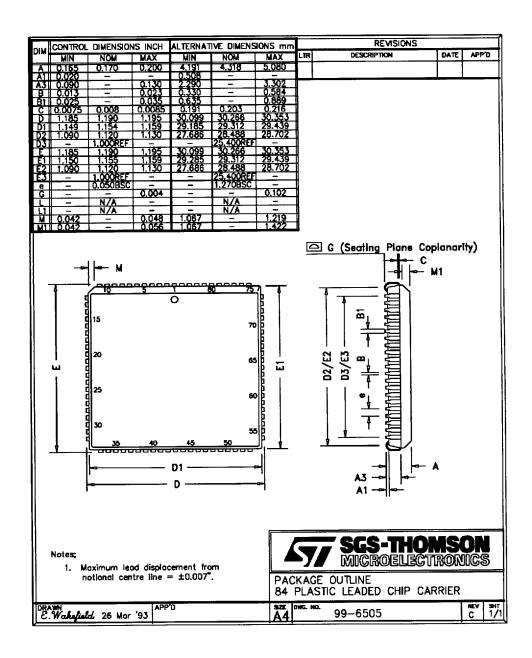


Figure 9.4 IMS T425 84-pin PLCC package dimensions

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9.3 100 pin plastic quad flat pack (PQFP) package

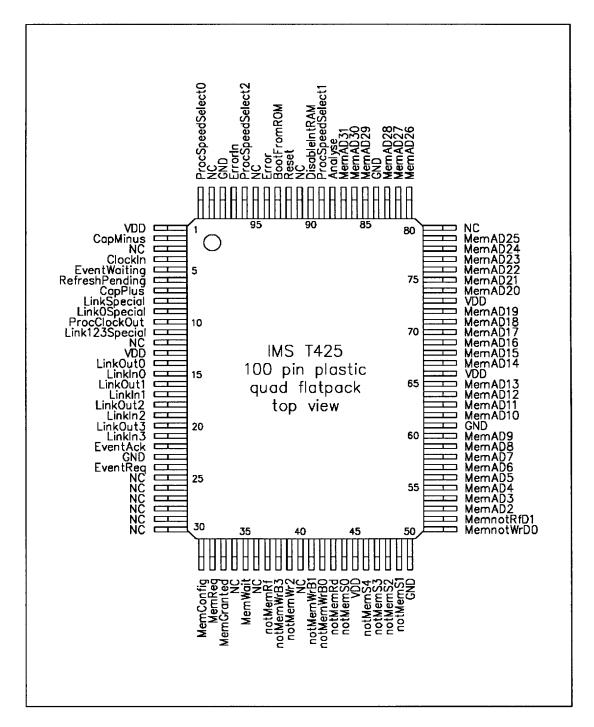


Figure 9.5 IMS T425 100-pin plastic quad flat pack (PQFP) package pinout

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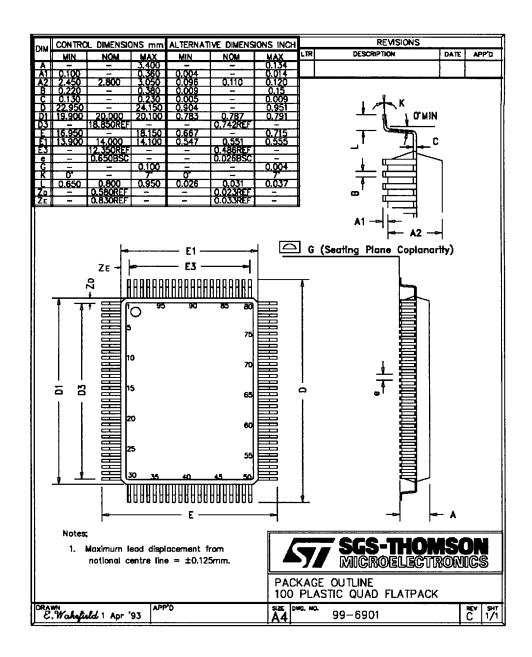


Figure 9.6 IMS T425 100-pin plastic quad flat pack (PQFP) package dimensions

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9.4 Thermal specification

The IMS T425 is tested to a maximum silicon temperature of 100°C. For operation within the given specifications, the case temperature should not exceed 85°C.

For temperatures above 85°C the operation of the device cannot be guaranteed and reliability may be impaired.

For further information on reliability refer to the SGS-THOMSON Microelectronics Quality and Reliability Program.

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10 Ordering

This section indicates the designation of speed and package selections for the various devices. Speed of **Clockin** is 5 MHz for all parts. Transputer processor cycle time is nominal; it can be calculated more exactly using the phase lock loop factor **PLLx**, as detailed in the external memory section.

For availability contact your local SGS-THOMSON sales office or authorized distributor.

SGS-THOMSON designation	Processor clock speed	Processor cycle time	PLLx	Package
IMS T425-G25S	25.0	40	5.0	84 pin ceramic pin grid array
IMS T425-J25S	25.0	40	5.0	84 pin plastic PLCC J-bend
IMS T425-X25S	25.0	40	5.0	100 pin plastic quad flat pack

Table 10.1 IMS T425 ordering details

11 Transputer instruction set summary

11.1 Introduction

The Function Codes table 11.9 (page 62) gives the basic function code set. Where the operand value is less than 16, a single byte encodes the complete instruction. If the operand value is greater than 15, one prefix instruction (pfix) is required for each additional four bits of the operand. If the operand is negative the first prefix instruction will be nfix. Examples of prefix coding are given in table 11.1.

Mne	emonic	Function code	Memory code		
ldc	#3	#4	#43		
ldc	#35				
is coded a	as				
pfix	#3	#2	#23		
ldc	#5	#4	#45		
ldc	#987				
is coded a	as				
pfix	#9	#2	#29		
pfix	#8	#2	#28		
ldc	#7	#4	#47		
ldc	-31	(/dc #FFFFFE1) (/dc #FFE1) †			
is coded a	as				
nfix	#1	#6	#61		
ldc	#1	#4	#41		
† IMS T222, IMS T225					

Table 11.1 prefix coding

Tables 11.10 to 11.30 (pages 62–69) give details of the operation codes. Where an operation code is less than 16 (e.g. *add.* operation code **05**), the operation can be stored as a single byte comprising the *operate* function code **F** and the operand (**5** in the example). Where an operation code is greater than 15 (e.g. *ladd.* operation code **16**), the *prefix* function code **2** is used to extend the instruction.

Mnemonic		Function code	Memory code
add	(op. code #5)		#F5
is coded	as		
opr	add	#F	# F 5
ladd	(op. code #16)		#21F6
is coded	as		
pfix	#1	#2	#21
opr	#6	#F	# F 6

Table 11.2 operate coding

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11.1.1 Product identity numbers

The load device identity (*Iddevid*) instruction (table 11.10) pushes the device type identity into the A register. Each product is allocated a unique group of numbers for use with the *Iddevid* instruction. Product identity numbers are given in table 11.3.

Product	Identity numbers
IMS T425	0 to 9 inclusive
IMS T805	10 to 19 inclusive
IMS T225	40 to 49 inclusive
IMS T400	50 to 59 inclusive

Table 11.3 Product identity numbers

11.1.2 Floating point unit

In the floating point unit (FPU) basic addition, subtraction, multiplication and division operations are performed by single instructions. However, certain less frequently used floating point instructions are selected by a value in register A (when allocating registers, this should be taken into account). A *load constant* instruction *ldc* is used to load register A; the *floating point entry* instruction *fpentry* then uses this value to select the floating point operation. This pair of instructions is termed a *selector sequence*.

In the Floating Point Operation Codes tables 11.23 to 11.29, a selector sequence code is indicated in the Memory Code column by **s**. The code given in the Operation Code column is the indirection code, the operand for the *Idc* instruction.

The FPU and processor operate concurrently, so the actual throughput of floating point instructions is better than that implied by simply adding up the instruction times. For full details see *Transputer Instruction Set – A Compiler Writer's Guide.*

11.1.3 Notation

The Processor Cycles column refers to the number of periods **TPCLPCL** (refer to **ProcClockOut**) taken by an instruction executing in internal memory. The number of cycles is given for the basic operation only; where the memory code for an instruction is two bytes, the time for the *prefix* function (one cycle) should be added. Some instruction times vary. Where a letter is included in the cycles column it is interpreted from table 11.4.

Ident	Interpretation
b	Bit number of the highest bit set in register A. Bit 0 is the least significant bit.
m †	Bit number of the highest bit set in the absolute value of register A . Bit 0 is the least significant bit.
n	Number of places shifted.
w	Number of words in the message. Part words are counted as full words. If the message is not word aligned the number of words is increased to include the part words at either end of the message.
p†	Number of words per row.
r†	Number of rows.
† does	not apply to IMS T225

Table 11.4 Instruction set interpretation

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The **DEF** column of the tables indicates the descheduling/error features of an instruction as described in table .

Ident	Feature See section					
D	The instruction is a descheduling point	11.2				
E	The instruction will affect the Error flag	11.3				
F†	The instruction will affect the FP_Error flag	11.6				
† applies	† applies to IMS T805 only					

Table 11.5 Instruction features

11.2 Descheduling points

The instructions in table 11.6 are the only ones at which a process may be descheduled. They are also the ones at which the processor will halt if the **Analyse** pin is asserted (refer to **Analyse** section).

input message	output message	output byte	output word	
timer alt wait	timer input	stop on error	alt wait	
jump	loop end	end process	start process	

Table 11.6 Descheduling point instructions

11.3 Error instructions

The instructions in table 11.7 are the only ones which can affect the *Error* flag directly. Note, however, that the floating point unit error flag *FP_Error* is set by certain floating point instructions (section 11.6), and that *Error* can be set from this flag by *fpcheckerror*.

add	add constant	subtract	····
multiply	fractional multiply †	divide	remainder
long add	long subtract	long divide	
set error	testerr	fpcheckerror‡	
check word	check subscript from 0	check single	check count from 1
† does not apply	to IMS T225		
‡ applies to IMS	T805 only		

Table 11.7 Error setting instructions

11.4 Debugging support

Table 11.20 (page 66) contains a number of instructions to facilitate the implementation of breakpoints. These instructions overload the operation of *j0*. Normally *j0* is a no-op which might cause descheduling. Setj0break enables the breakpointing facilities and causes *j0* to act as a breakpointing instruction. When breakpointing is enabled, *j0* swaps the current **lptr** and **Wptr** with an **lptr** and **Wptr** stored above MemStart. The break instruction does not cause descheduling, and preserves the state of the registers. It is possible to single step the processor at machine level using these instructions. Refer to Support for debugging/breakpointing in transputers (technical note 61) for more detailed information regarding debugger support.

11.5 Block move

The block move instructions (Table 11.21) move any number of bytes from any byte boundary in memory, to any other byte boundary, using the smallest possible number of word read, and word or part-word writes.

 A block move instruction can be interrupted by a high priority process. On interrupt, block move is completed to a word boundary, independent of start position. When restarting after interrupt, the last word written is written again. This appears as an unnecessary read and write in the simplest case of word aligned block moves, and may cause problems with FIFOs. This problem can be overcome by incrementing the saved destination (**BregIntSaveLoc**) and source pointer (**CregIntSaveLoc**) values by BytesPerWord during the high priority process.

11.6 Floating point errors (IMS T805 only)

The FPU has its own error flag *FP_Error*. This reflects the state of evaluation within the FPU and is set in circumstances where invalid operations, division by zero or overflow exceptions to the ANSI-IEEE 754-1985 standard would be flagged. *FP_Error* is also set if an input to a floating point operation is infinite or is not a number (NaN). The *FP_Error* flag can be set, tested and cleared without affecting the main *Error* flag, but can also set *Error* when required. Depending on how a program is compiled, it is possible for both unchecked and fully checked floating point arithmetic to be performed.

The instructions in table 11.8 are the only ones which can affect the floating point error flag *FP_Error*. *Error* is set from this flag by *fpcheckerror* if *FP_Error* is set.

fpadd	fpsub	fpmul	fpdiv
fpldnladdsn	fpldnladddb	fpldnlmulsn	fpldnlmuldb
fpremfirst	fpusqrtfirst	fpgt	fpeq
fpuseterror	fpuclearerror	fptesterror	
fpuexpincby32	fpuexpdecby32	fpumulby2	fpudivby2
fpur32tor64	fpur64tor32	fpucki32	fpucki64
fprtoi32	fpuabs	fpint	

Table 11.8 Floating point error setting instructions

11.7 General instructions

The following tables list the complete instruction set which is common to all variants of the transputer. Exceptions are noted at the bottom of each table by or ‡.

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Function Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
0	0X	j	3	jump	D
1	1X	ldlp	1	load local pointer	
2	2X	pfix	1	prefix	
3	3X	Idni	2	load non-local	
4	4X	ldc	1	load constant	
5	5X	Idnlp	1	load non-local pointer	
6	6X	nfix	1	negative prefix	
7	7X	ldl	2	load local	
8	8X	adc	1	add constant	E
9	9X	call	7	call	
Α	AX	cj	2	conditional jump (not taken)	
			4	conditional jump (taken)	
В	BX	ajw	1	adjust workspace	
С	CX	eqc	2	equals constant	
D	DX	stl	1	store local	
E	EX	stnl	2	store non-local	
F	FX	opr	_	operate	

Table 11.9 Function codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
2A	22FA	testpranal	2	test processor analyzing	
3E	23FE	saveh	4	save high priority queue registers	
3D	23FD	savel	4	save low priority queue registers	
18	21F8	sthf	1	store high priority front pointer	
50	25F0	sthb	1	store high priority back pointer	
1C	21FC	stlf	1	store low priority front pointer	
17	21F7	stib	1	store low priority back pointer	
54	25F4	sttimer	1	store timer	
17C	2127FC	Iddevid	1	load device identity	
7E	27FE	Idmemstartval	1	load value of memstart address	

Table 11.10 Processor initialisation operation codes

Operation	Memory	Mnemonic	Processo	r Cycles	Name	DEF	
Code	Code		16-bit devices	32-bit devices			
46	24F6	and	1	1	and		
4B	24FB	or	1	1	or		
33	23F3	xor	1	1	exclusive or		
32	23F2	not	1	1	bitwise not	1	
41	24F1	shl	n +2	n+2	shift left	1	
40	24F0	shr	n +2	n+2	shift right		
05	F5	add	1	1	add	E	
0C	FC	sub	1	1	subtract	E	
53	25F3	mul	23	38	multiply	E	
72	27F2	fmul	:	35	fractional multiply (no rounding)	İΕ	
				40	fractional multiply (rounding)	E	
2C	22FC	div	24	39	divide	E	
1F	21FF	rem	21	37	remainder	E	
09	F9	gt	2	2	greater than		
04	F4	diff	1	1	difference		
52	25F2	sum	1	1	sum		
08	F8	prod	b+4	b+4	product for positive register A		
08	F8	prod	m+5	m +5	product for negative register A		
† does not a	† does not apply to IMS T225						

Table 11.11 Arithmetic/logical operation codes

Operation	Memory	Mnemonic	Processo	r Cycles	Name	DEF
Code	Code		16-bit devices	32-bit devices		
16	21F6	ladd	2	2	long add	E
38	23F8	Isub	2	2	long subtract	E
37	23F7	Isum	3	3	long sum	
4F	24FF	Idiff	3	3	long diff	
31	23F1	lmul	17	33	long multiply	
1A	21FA	ldiv	19	35	long divide	E
36	23F6	ishl	n+3	n+3	long shift left (n<32) † (n<1	3)
•		ļ	n-12	n-28	long shift left(n 32) † (n 1	5)
35	23F5	Ishr	n+3	n+3	long shift right (n<32) † (n<1	3)
			n-12	n-28	long shift right (n 32) † (n 1	3)
19	21F9	norm	n +5	n +5	normalise (n<32) † (n<1	6)
		}	n-10	n-26	normalise (n 32) † (n 1	6)
			3	3	normalise (n=64) † (n=3	2)
† for IMS 7	T225					

Table 11.12 Long arithmetic operation codes



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Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
00	F0	rev	1	reverse	
3A	23FA	xword	4	extend to word	
56	25F6	cword	5	check word	E
1D	21FD	xdble	2	extend to double	
4C	24FC	csngl	3	check single	E
42	24F2	mint	1	minimum integer	
5A	25FA	dup	1	duplicate top of stack	
79	27 F 9	рор	1	pop processor stack	

Table 11.13 General operation codes

Operation	Memory	Mnemonic	Processo	r Cycles	Name	DEF
Code	Code		16-bit devices	32-bit devices		
02	F2	bsub	1	1	byte subscript	
0A	FA	wsub	2	2	word subscript	
81 †	28F1	wsubdb	3	3	form double word subscript	
34	23F4	bent	2	2	byte count	
3F	23FF	wcnt	4	5	word count	:
01	F1	lb	5	5	load byte	
3B	23FB	sb	4	4	store byte	
4A	24FA	move	2 w +8	2 w +8	move message	
† does not a	apply to IM:	S T225				•

Table 11.14 Indexing/array operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
22	22F2	ldtimer	2	load timer	
2B	22FB	tin	30	timer input (time future)	D
			4	timer input (time past)	D
4E	24FE	talt	4	timer alt start	
51	25F1	taltwt	15	timer alt wait (time past)	D
			48	timer alt wait (time future)	D
47	24F7	enbt	8	enable timer	
2 E	22FE	dist	23	disable timer	

Table 11.15 Timer handling operation codes

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Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
07	F7	in	2 w +19	input message	D
0B	FB	out	2 w +19	output message	D
OF	FF	outword	23	output word	D
0E	FE	outbyte	23	output byte	D
43	24F3	alt	2	alt start	
44	24F4	altwt	5	alt wait (channel ready)	D
			17	alt wait (channel not ready)	D
45	24F5	altend	4	alt end	
49	24F9	enbs	3	enable skip	
30	23F0	diss	4	disable skip	
12	21F2	resetch	3	reset channel	
48	24F8	enbc	7	enable channel (ready)	
			5	enable channel (not ready)	
2F	22FF	disc	8	disable channel	

Table 11.16 Input/output operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
20	22F0	ret	5	return	
1B	21FB	ldpi	2	load pointer to instruction	
3C	23FC	gajw	2	general adjust workspace	
06	F6	gcall	4	general call	
21	22F1	lend	10	loop end (loop)	D
			5	loop end (exit)	D

Table 11.17 Control operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
0D	FD	startp	12	start process	
03	F3	endp	13	end process	D
39	23F9	runp	10	run process	
15	21F5	stopp	11	stop process	
1E	21FE	ldpri	1	load current priority	

Table 11.18 Scheduling operation codes



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Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
13	21F3	csub0	2	check subscript from 0	E
4D	24FD	ccnt1	3	check count from 1	E
29	22F9	testerr	2	test error false and clear (no error)	
		,	3	test error false and clear (error)	
10	21F0	seterr	1	set error	E
55	25F5	stoperr	2	stop on error (no error)	D
57	25F7	cirhaiterr	1	clear halt-on-error	
58	25F8	sethalterr	1	set halt-on-error	
59	25 F 9	testhalterr	2	test halt-on-error	

Table 11.19 Error handling operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
0	00	jump 0	3	jump 0 (break not enabled)	D
ļ			11	jump 0 (break enabled, high priority)	
]			13	jump 0 (break enabled, low priority)	
B1	2BF1	break	9	break (high priority)	
			11	break (low priority)	
B2	2BF2	clrj0break	1	clear jump 0 break enable flag	
В3	2BF3	setj0break	1	set jump 0 break enable flag	
B4	2BF4	testj0break	2	test jump 0 break enable flag set	
7A	27FA	timerdisableh	1	disable high priority timer interrupt	
7B	27FB	timerdisablel	1	disable low priority timer interrupt	
7C	27FC	timerenableh	6	enable high priority timer interrupt	
7D	27FD	timerenablel	6	enable low priority timer interrupt	

Table 11.20 Debugger support codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
5B †	25FB	move2dinit	8	initialise data for 2D block move	
5C †	25FC	move2dall	(2 p +23)r	2D block copy	
5D †	25FD	move2dnonzero	(2 p +23) r	2D block copy non-zero bytes	
5E †	25FE		(2 p +23) r	2D block copy zero bytes	
† does not a	pply to IMS	T225		,	

Table 11.21 2D block move operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
74	27F4	crcword	35	calculate crc on word	
75	27 F 5	crcbyte	11	calculate crc on byte	
76	27 F 6	bitcnt	b +2	count bits set in word	
77	27 F 7	bitrevword	36	reverse bits in word	
78	27F8	bitrevnbits	n+4	reverse bottom n bits in word	

Table 11.22 CRC and bit operation codes

11.8 Floating point instructions

11.9 Floating point instructions for IMS T805 only

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF		
8E	28FE	fpldnlsn	2	fp load non-local single			
8A	28FA	fpldnldb	3	fp load non-local double			
86	28F6	fpldnlsni	4	fp load non-local indexed single			
82	28F2	fpldnldbi	6	fp load non-local indexed double			
9F	29FF	fpldzerosn	2	load zero single			
A0	2AF0	fpldzerodb	2	load zero double			
AA	2AFA	fpldnladdsn	8/11	fp load non local & add single	F		
A6	2AF6	fpldnladddb	9/12	fp load non local & add double	F		
AC	2AFC	fpldnlmulsn	13/20	fp load non local & multiply single	F		
A8	2AF8	fpldnlmuldb	21/30	fp load non local & multiply double	F		
88	28F8	fpstnlsn	2	fp store non-local single			
84	28F4	fpstnldb	3	fp store non-local double			
9E	29FE	fpstnli32	4	store non-local int32			
Processor cyc	Processor cycles are shown as Typical/Maximum cycles.						

Table 11.23 Floating point load/store operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
AB	2AFB	fpentry	1	floating point unit entry	
A4	2AF4	fprev	1	fp reverse	
А3	2AF3	fpdup	1	fp duplicate	

Table 11.24 Floating point general operation codes

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Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
22	s	fpurn	1	set rounding mode to round nearest	
06	s	fpurz	1	set rounding mode to round zero	
04	s	fpurp	1	set rounding mode to round positive	
05	s	fpurm	1	set rounding mode to round minus	

Table 11.25 Floating point rounding operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
83	28F3	fpchkerror	1	check fp error	E
9C	29FC	fptesterror	2	test fp error false and clear	F
23	s	fpuseterror	1	set fp error	F
9C	s	fpuclearerror	1	clear fp error	F

Table 11.26 Floating point error operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF	
94	29 F 4	fpgt	4/6	fp greater than	F	
95	29 F 5	fpeq	3/5	fp equality	F	
92	29F2	fpordered	3/4	fp orderability		
91	29F1	fpnan	2/3	fp NaN		
93	29F3	fpnotfinite	2/2	fp not finite		
0E	s	fpuchki32	3/4	check in range of type int32	F	
0F	s	fpuchki64	3/4	check in range of type int64	F	
Processor cycles are shown as Typical/Maximum cycles.						

Table 11.27 Floating point comparison operation codes

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF
07	s	fpur32tor64	3/4	real32 to real64	F
80	s	fpur64tor32	6/9	real64 to real32	F
9D	29FD	fprtoi32	7/9	real to int32	F
96	29F6	fpi32tor32	8/10	int32 to real32	·
98	29F8	fpi32tor64	8/10	int32 to real64	
9 A	29FA	fpb32tor64	8/8	bit32 to real64	
0D	s	fpunoround	2/2	real64 to real32, no round	
A1	2AF1	fpint	5/6	round to floating integer	F

Table 11.28 Floating point conversion operation codes

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Operation	Memory		Processo	or Cycles		
Code	Code	Mnemonic	Single	Double	Name	DEF
87	28F7	fpadd	6/9	6/9	fp add	F
89	28 F 9	fpsub	6/9	6/9	fp subtract	F
8B	28FB	fpmul	11/18	18/27	fp multiply	F
8C	28FC	fpdiv	16/28	31/43	fp divide	F
0B	s	fpuabs	2/2	2/2	fp absolute	F
8F	28FF	fpremfirst	36/46	36/46	fp remainder first step	F
90	29F0	fpremstep	32/36	32/36	fp remainder iteration	
01	s	fpusqrtfirst	27/29	27/29	fp square root first step	F
02	s	fpusqrtstep	42/42	42/42	fp square root step	
03	s	fpusqrtlast	8/9	8/9	fp square root end	
OA	s	fpuexpinc32	6/9	6/9	multiply by 232	F
09	s	fpuexpdec32	6/9	6/9	divide by 2 ³²	F
12	s	fpumulby2	6/9	6/9	multiply by 2.0	F
11	s	fpudivby2	6/9	6/9	divide by 2.0	F
Processor cycles are shown as Typical/Maximum cycles.						

Table 11.29 Floating point arithmetic operation codes

11.10 Floating point instructions for IMS T400 and IMS T425 only

Operation Code	Memory Code	Mnemonic	Processor Cycles	Name	DEF		
73	27F3	cflerr	3	check floating point error	Е		
9C	29FC	fptesterr	1	load value true (FPU not present)			
63	26F3	unpacksn	15	unpack single length fp number			
6D	26FD	roundsn	12/15	round single length fp number			
6C	26FC	postnormsn	5/30	post-normalise correction of single length fp number			
71	27F1	ldinf	1	load single length infinity			
Processor cyc	Processor cycles are shown as Typical/Maximum cycles.						

Table 11.30 Floating point support operation codes

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